

Prototype of SiC beam monitor for the COMET experiment at J-PARC

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- SiC sensors for MIP detectors at COMET muon experiment @ J-PARC (Japan Proton Accelerator Research Complex)
 - Basic properties of the PN-devices
 - Overview of the COMET experiment
 - Concept of muon beam monitor based on SiC
 - Test beam results
 - Future prospect

Introduction

- SiC and diamond are more radiation-hard than standard n-type Si, 10^{14} n_{eq}/cm^2 for SiC and 10^{15} n_{eq}/cm^2 for diamond.
- Uniform device characteristics and productivity are still challenging.

Property	Diamond	GaN	4H-SiC	Si	Ge	CdTe	CdZnTe
E_g [eV]	5.5	3.39	3.26	1.12	0.67	1.44	1.60
$E_{breakdown}$ [V/cm]	10^7	4×10^6	2.2×10^6	3×10^5	10^5	TBD	TBD
μ_e [cm^2/Vs]	1800	100	800	1450	<3900 ^[2]	1090 ^[1]	906 ^[3]
μ_h [cm^2/Vs]	1200	30	115	450	<1900	110	-
v_{sat} [cm/s]	2.2×10^7	-	2×10^7	0.8×10^7	0.74×10^7 ^[5]	10^7	10^7
Z	6	31/7	14/6	14	32	48/52	48/52/30
ϵ_r (dielectric const.)	5.7	9.6	9.7	11.7	TBD	TBD	TBD
e-h energy [eV]	13	8.9	7.6-8.4	3.6	2.9	4.5	5.0
Density	3.515	6.15	3.22	2.33	5.3	5.9	5.8
Displacem. [eV]	43	20	25	13-20	15-18	5.3-6.2 ^[4]	-

low leakage current

high radiation-tolerance

small signal charges

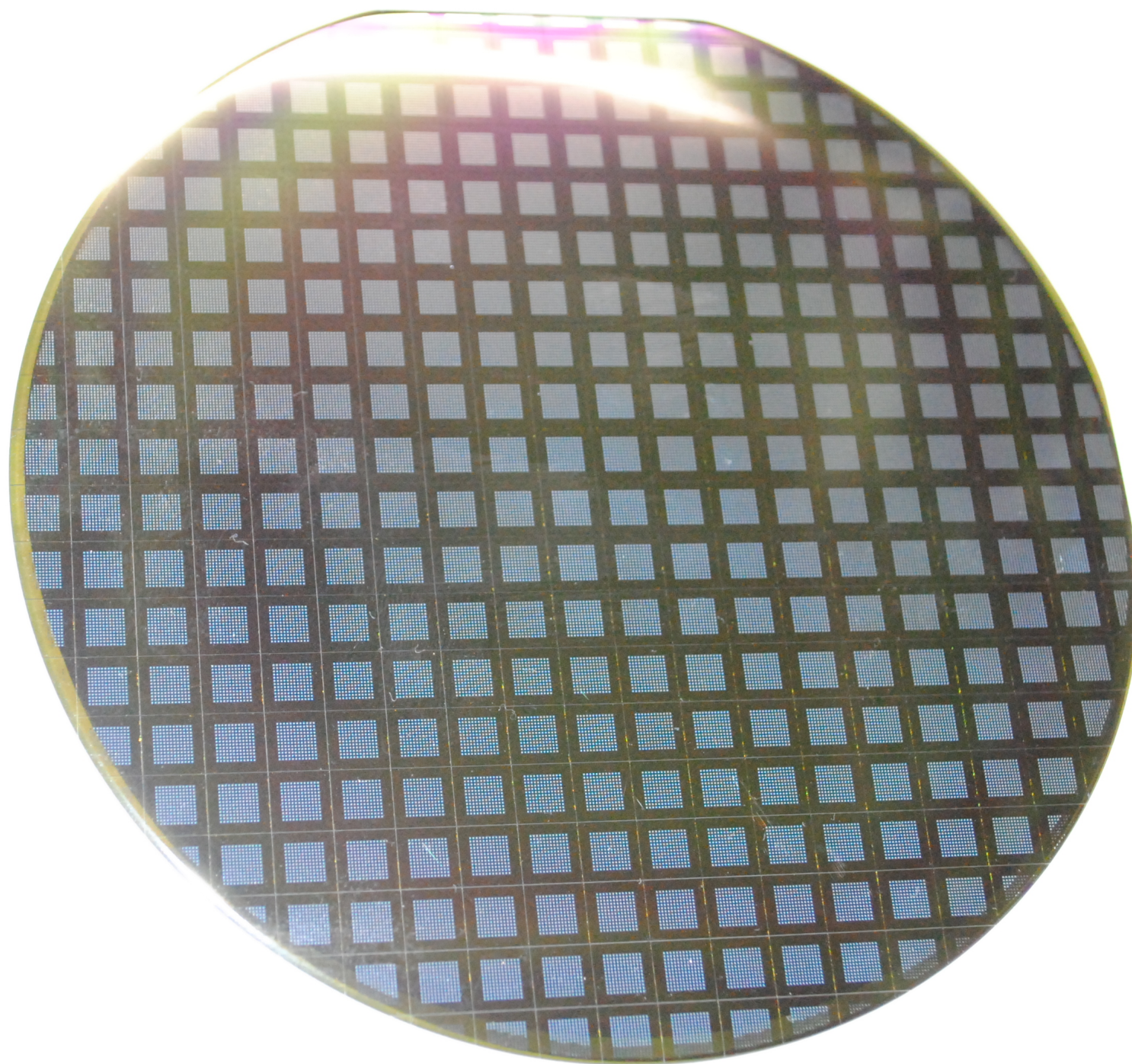
For stable device production, KEK-Esys collaborates with AIST power device group since 2019.

SiC device fabrication

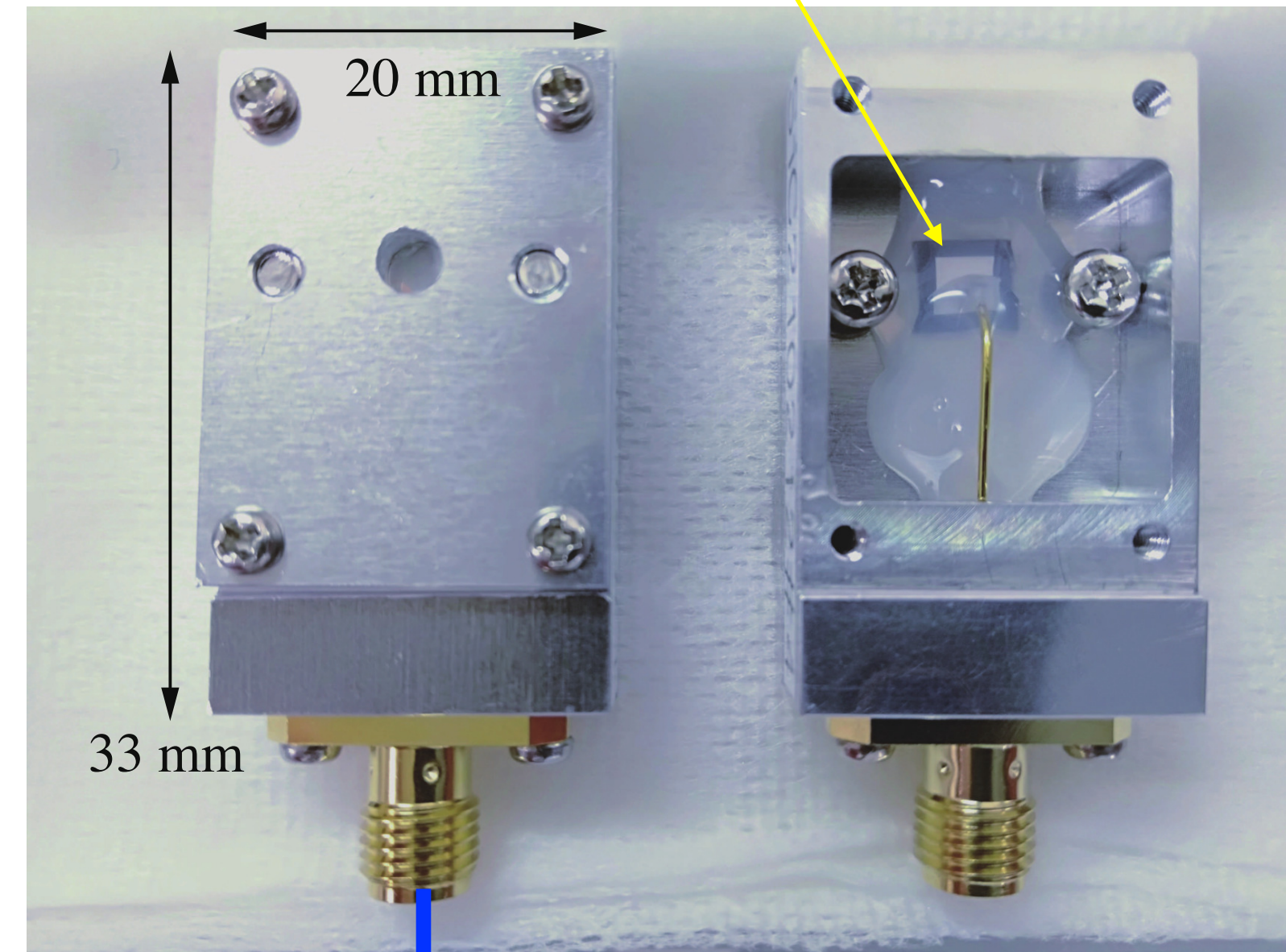
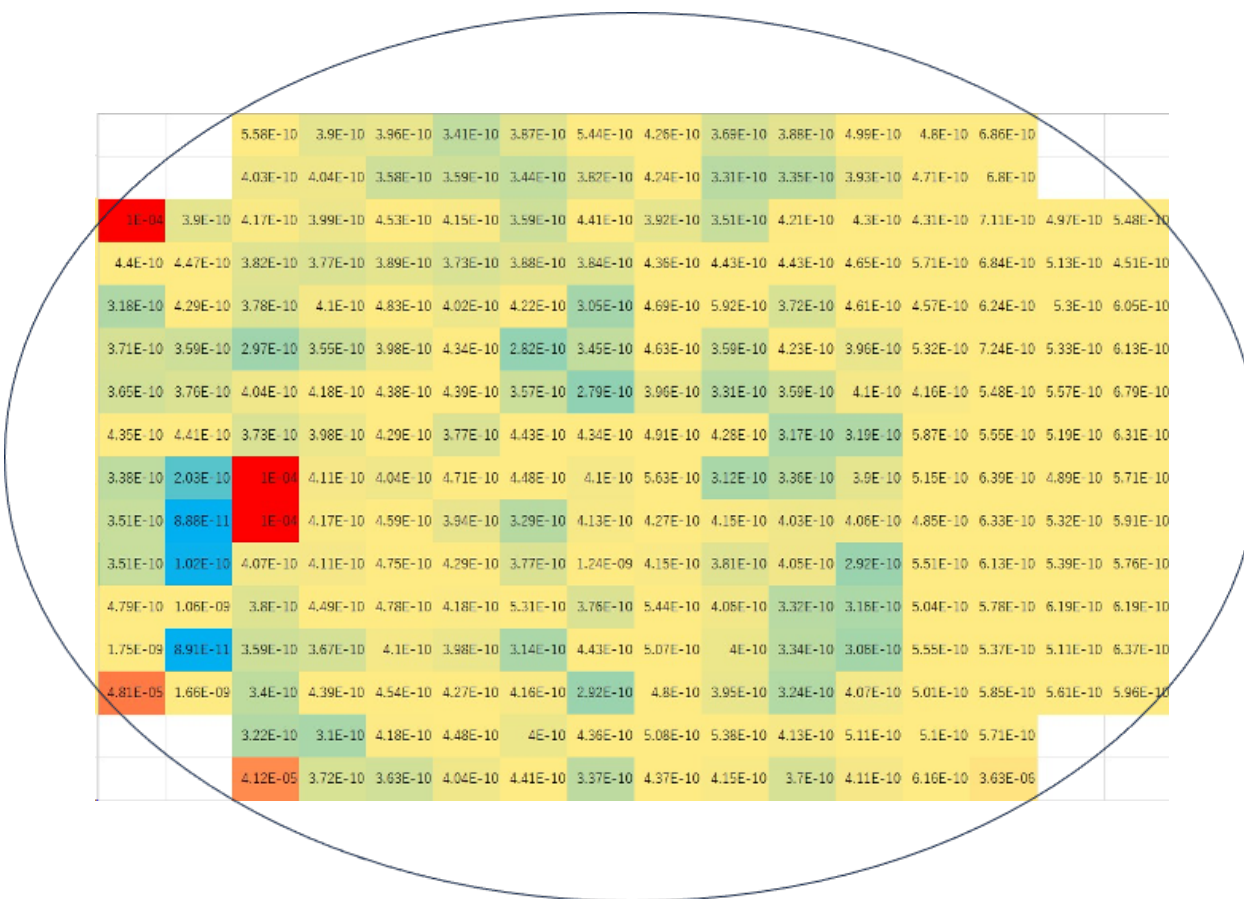
- PN diodes in wafer process, 5 mm x 5 mm simple diode
- Reverse bias tolerance of 3 kV
- 50 um epi grown on (0001) 4H-SiC n-type substrate @AIST
- Nd-Na: $4.7 \times 10^{14} \text{ cm}^{-3}$
- Thickness: 350 um
- 260 dies with $5 \times 5 \text{ mm}^2$ from 4-inch wafer, $4 \times 4 \text{ mm}^2$ active area

Schottky diode	PN diode
- Easy process	- Difficult process (High temperature annealing)
- Sensitive to surface conditions	- Less sensitive to surface conditions

Silicone rubber for preventing electric discharges



Color map of leakage currents

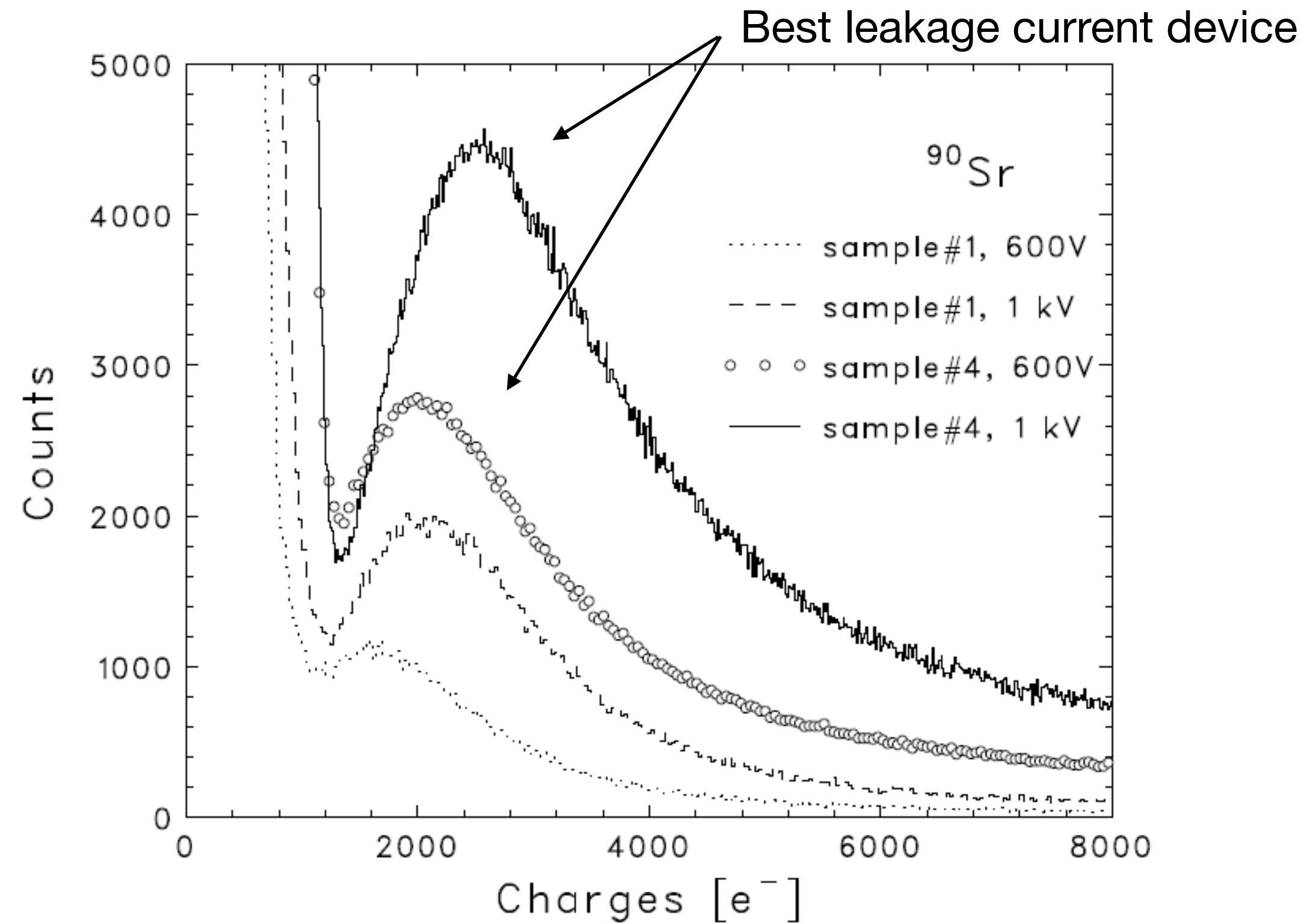


commercial CSA (AC-coupling)+shaper

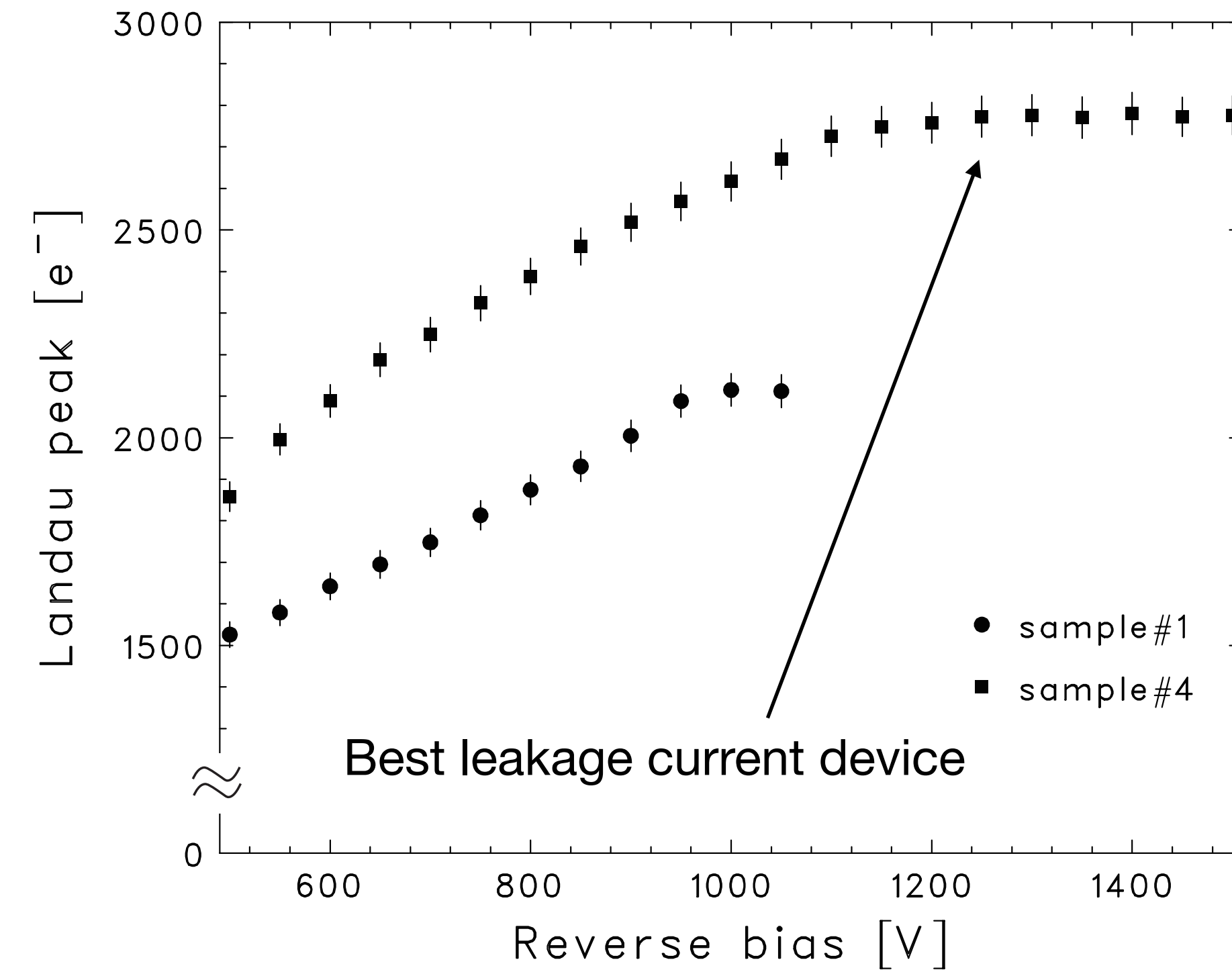
Device characteristics

- Leakage current <10 nA, uniform within one order of magnitude
- Stable Landau peak position (no polarization/charge-up)
- Full depletion voltage 1000 V for 50 um epi (TCAD)
- No signal / leakage current degradation, even after $10e+13$ n_{1MeV}/cm², even with biasing

IEEE TNS, vol.68, p.2787, 2021.



Landau peak is separated from pedestal in worst leakage device.

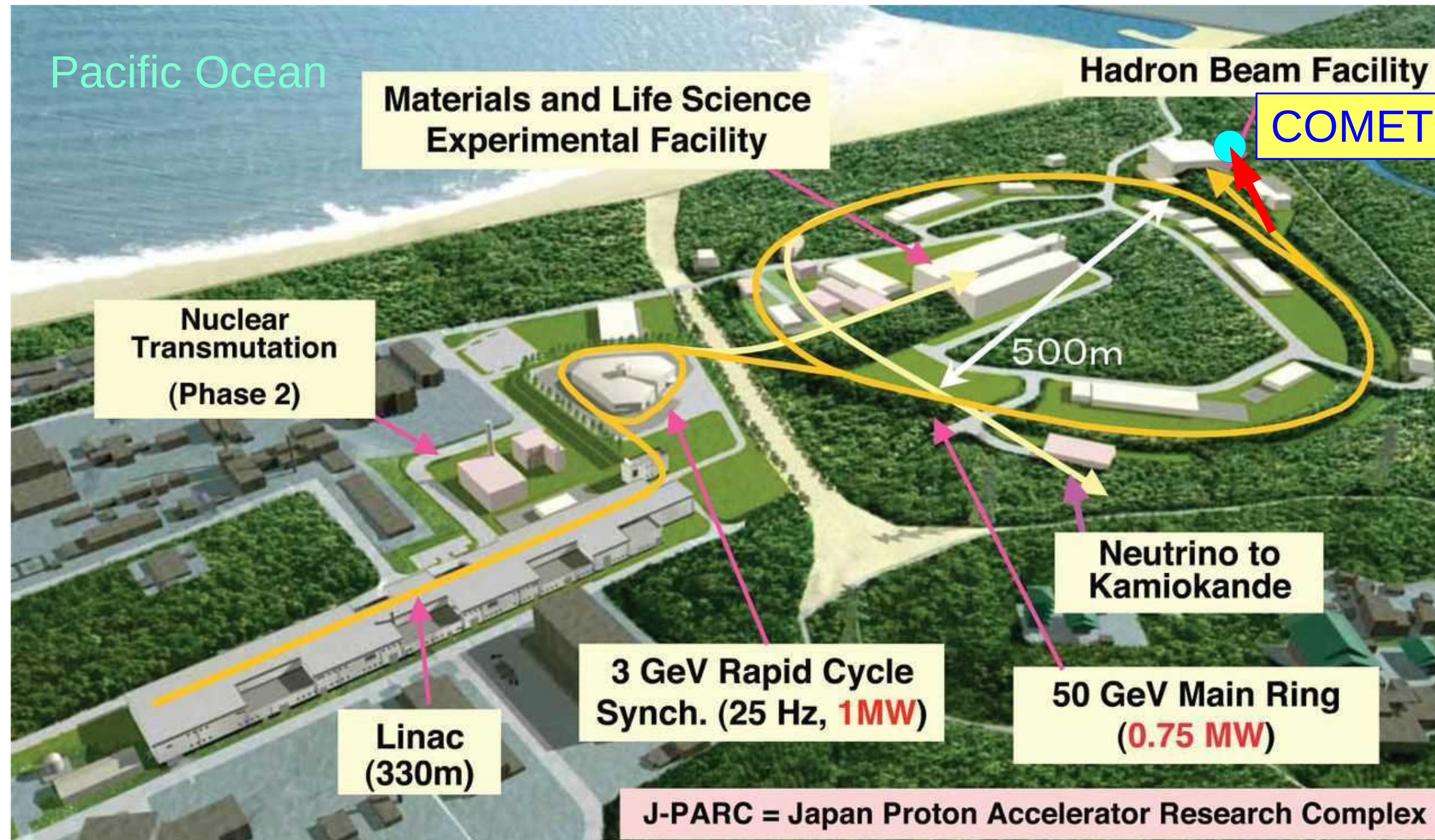


Full-depletion voltage is consistent with TCAD simulation.

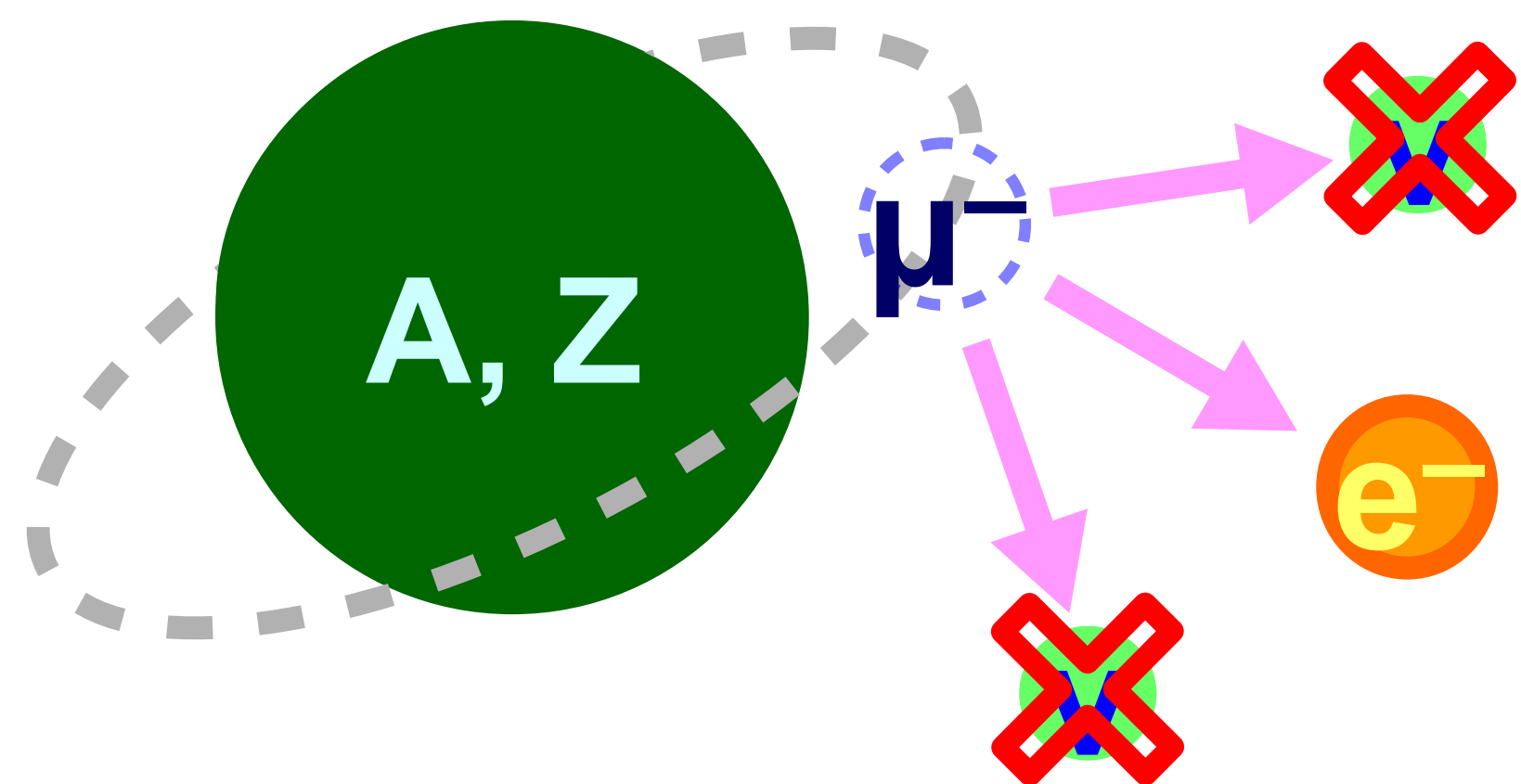
How can we play with these devices?

Demand for SiC sensor: COMET at J-PARC

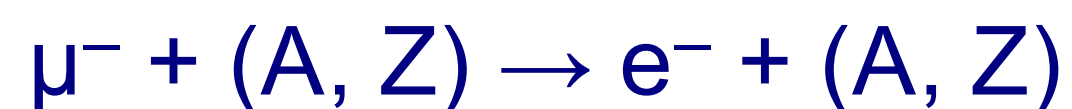
- COMET (COherent Muon to Electron Transition) starts from 2027 (one of the KEK core projects)
- They require **rad-hard beam monitors** for high-intensity 8 GeV protons / secondary particles



What do we do in COMET: Muon to Electron Transition

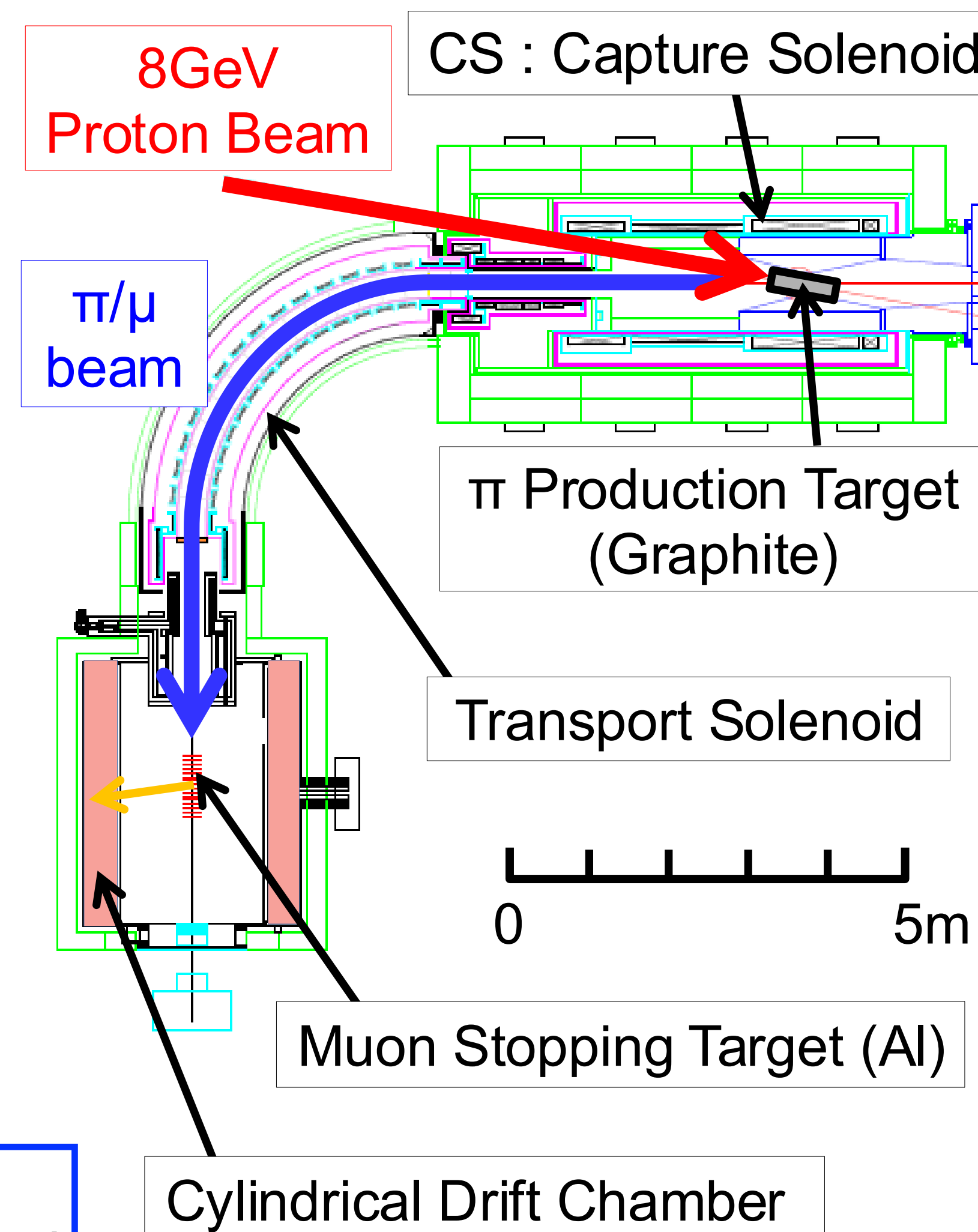


Search for neutrino-less muon to electron conversion.



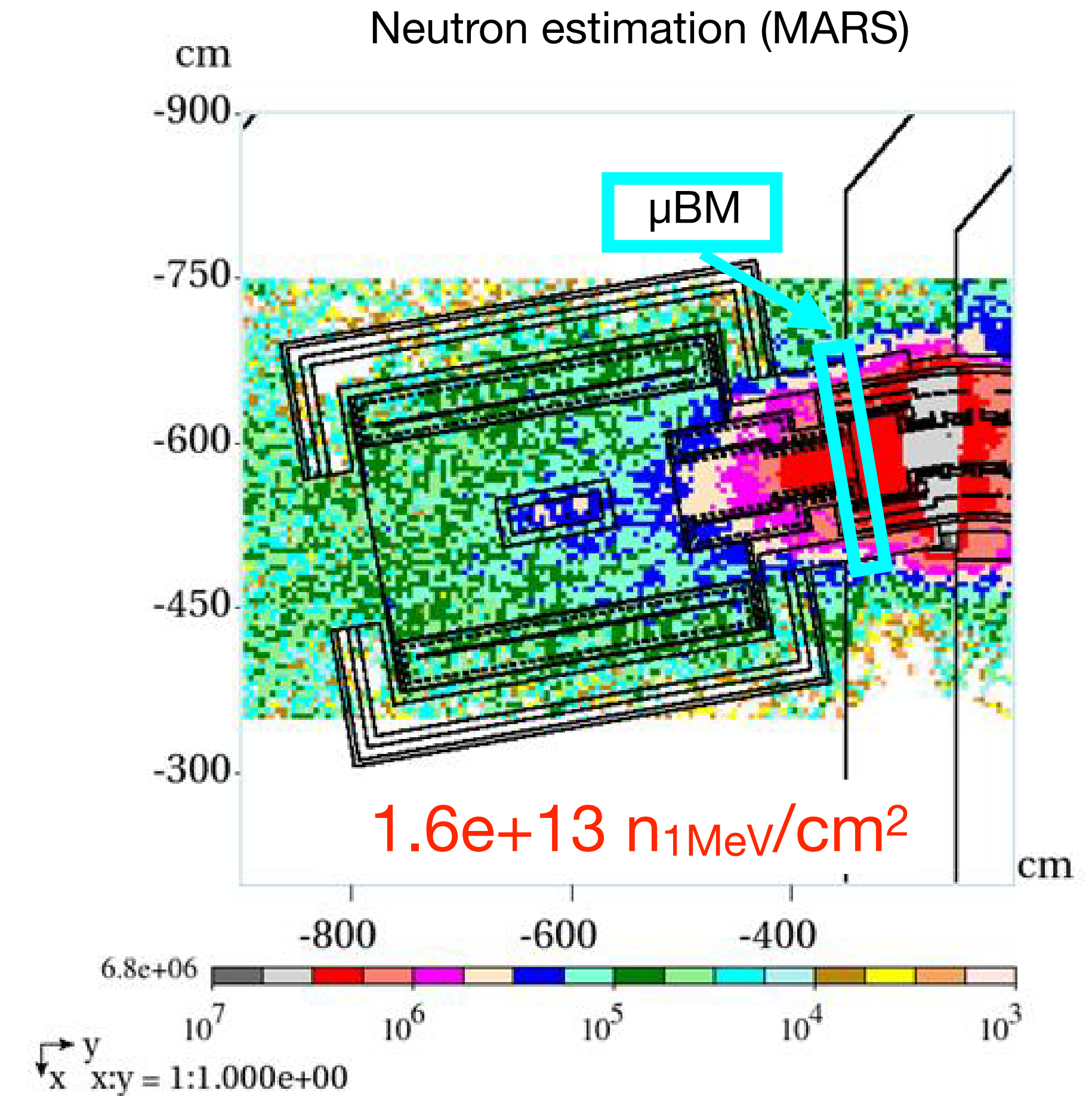
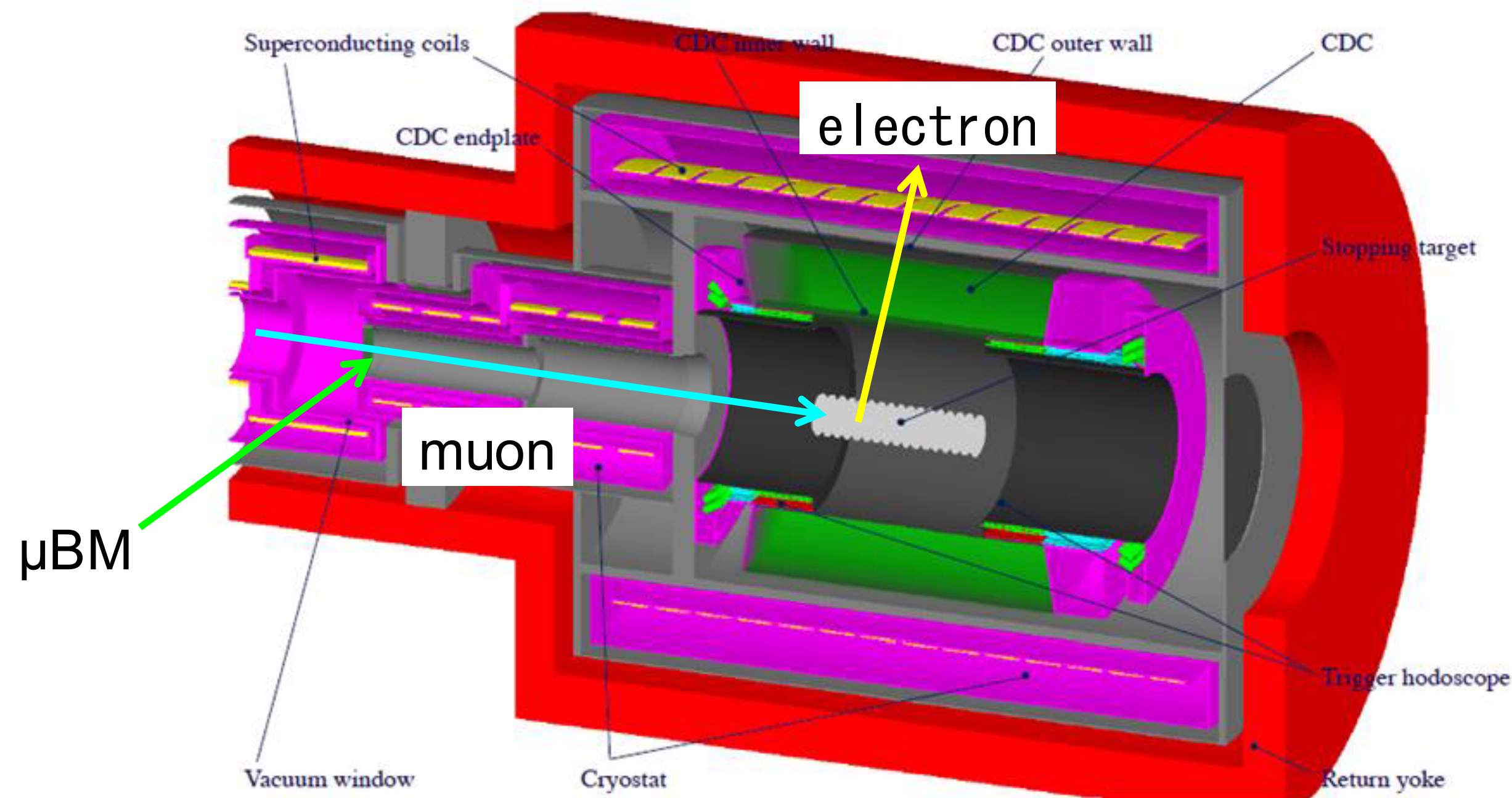
Contribution from Standard Model by neutrino oscillation is $\sim O(10^{-54})$.
 Good probe for new physics search.

- COMET aims to achieve **x100 higher sensitivity** from the past.
- It's good opportunity to install "own" detectors to contribute to new physics!



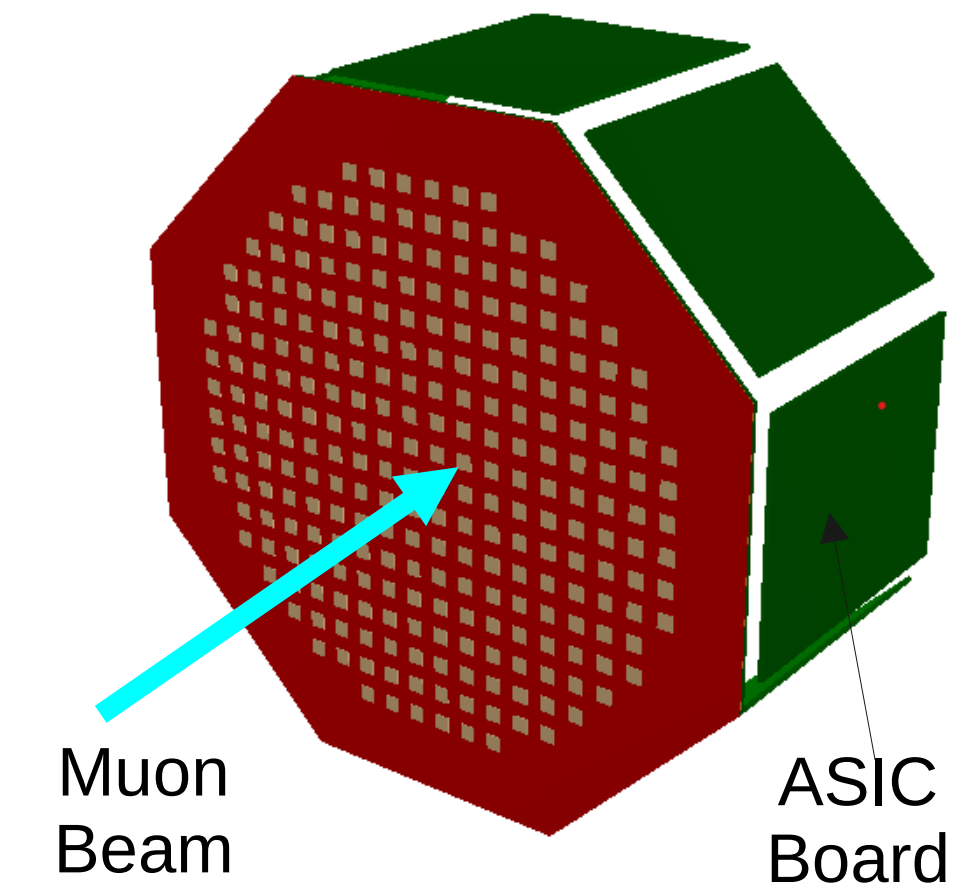
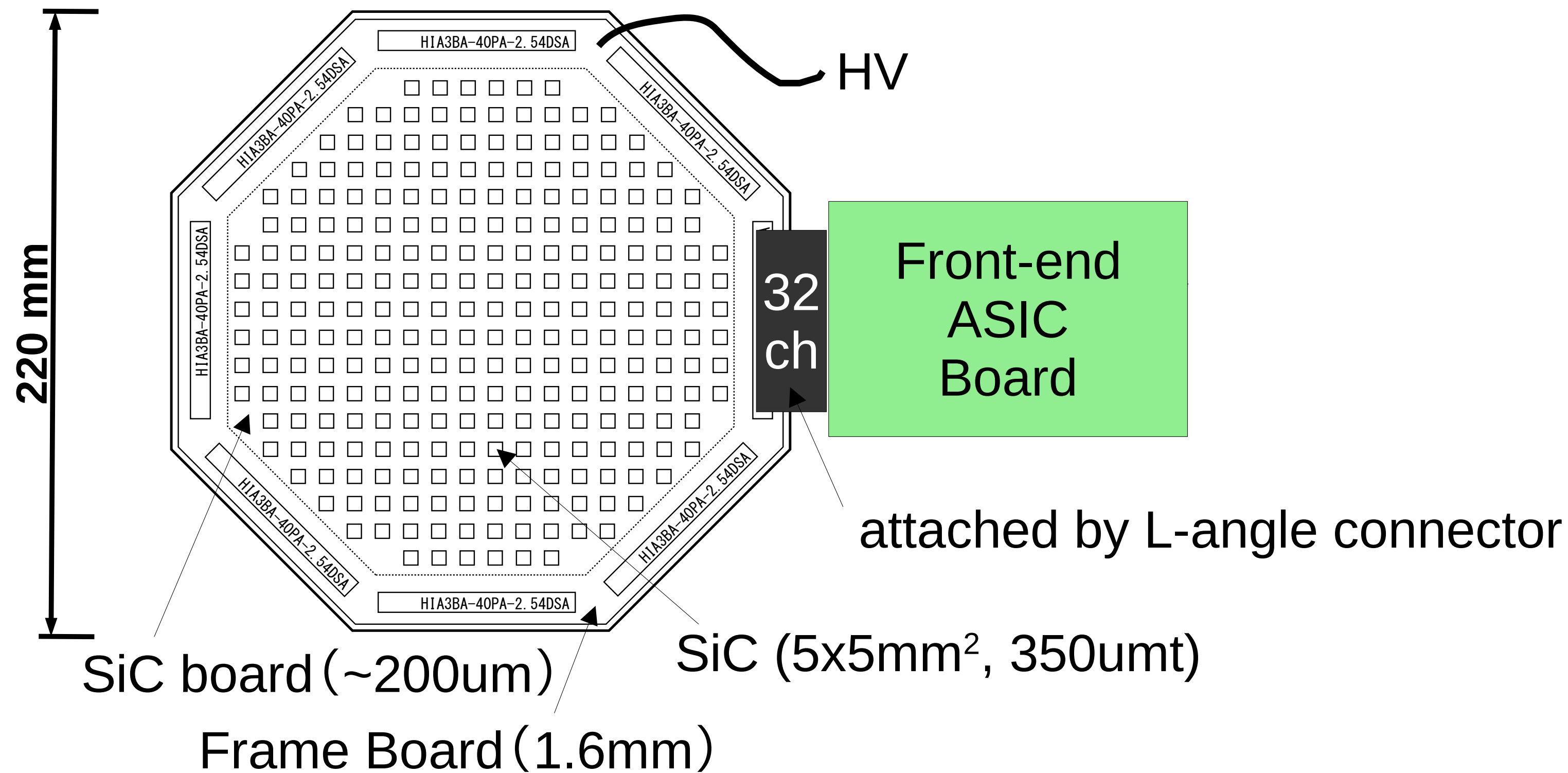
COMET Phase-1 and muon beam monitor (μ BM)

- Pions decay to muons during transportation in Solenoid magnet.
- Muons are decayed into electrons in the stopping target.
- Beam profile monitor, bunch stability, ToF background estimation etc.



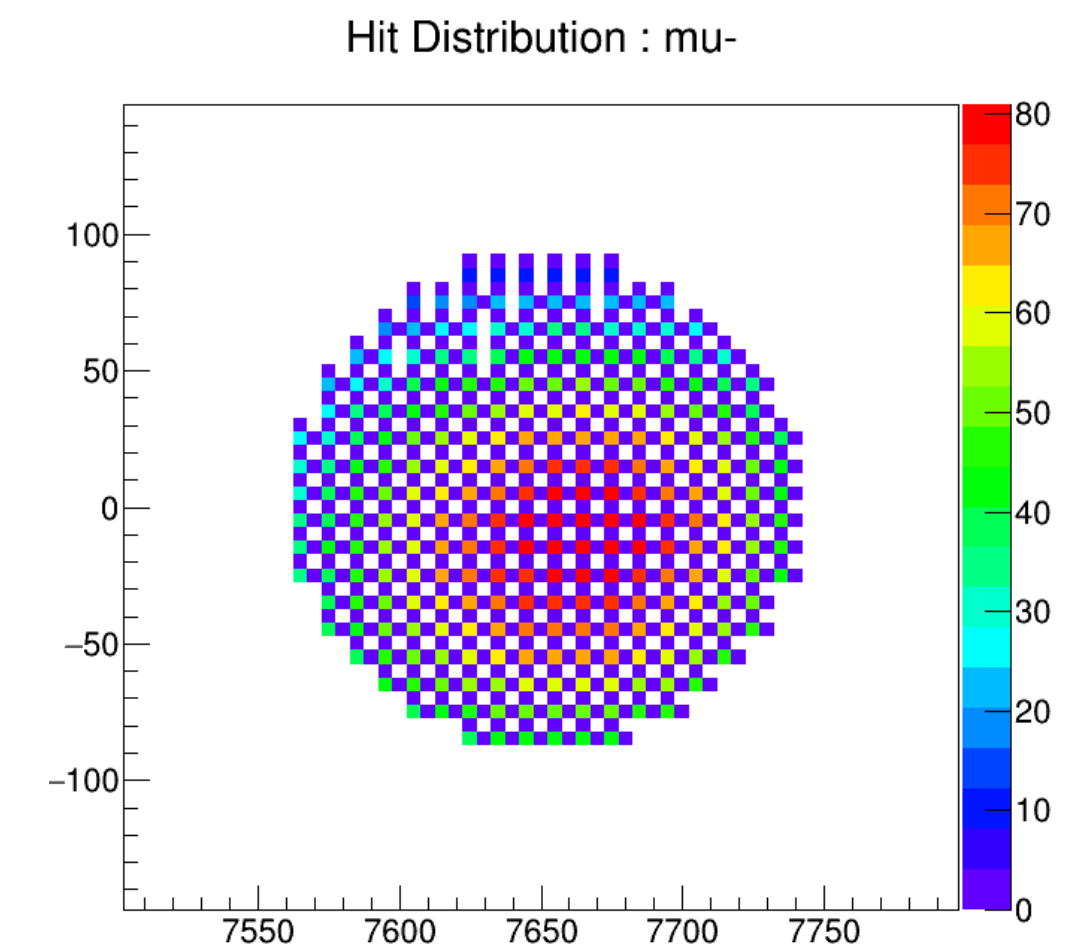
- Radiation-tolerance is the key to the muon beam monitor.

Concept of SiC-based μ BM



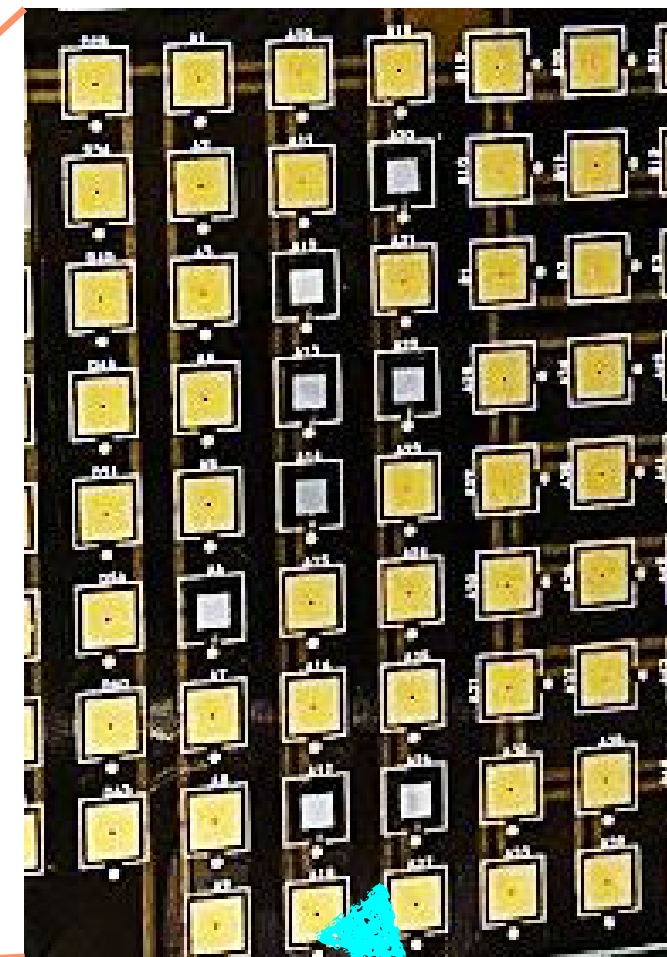
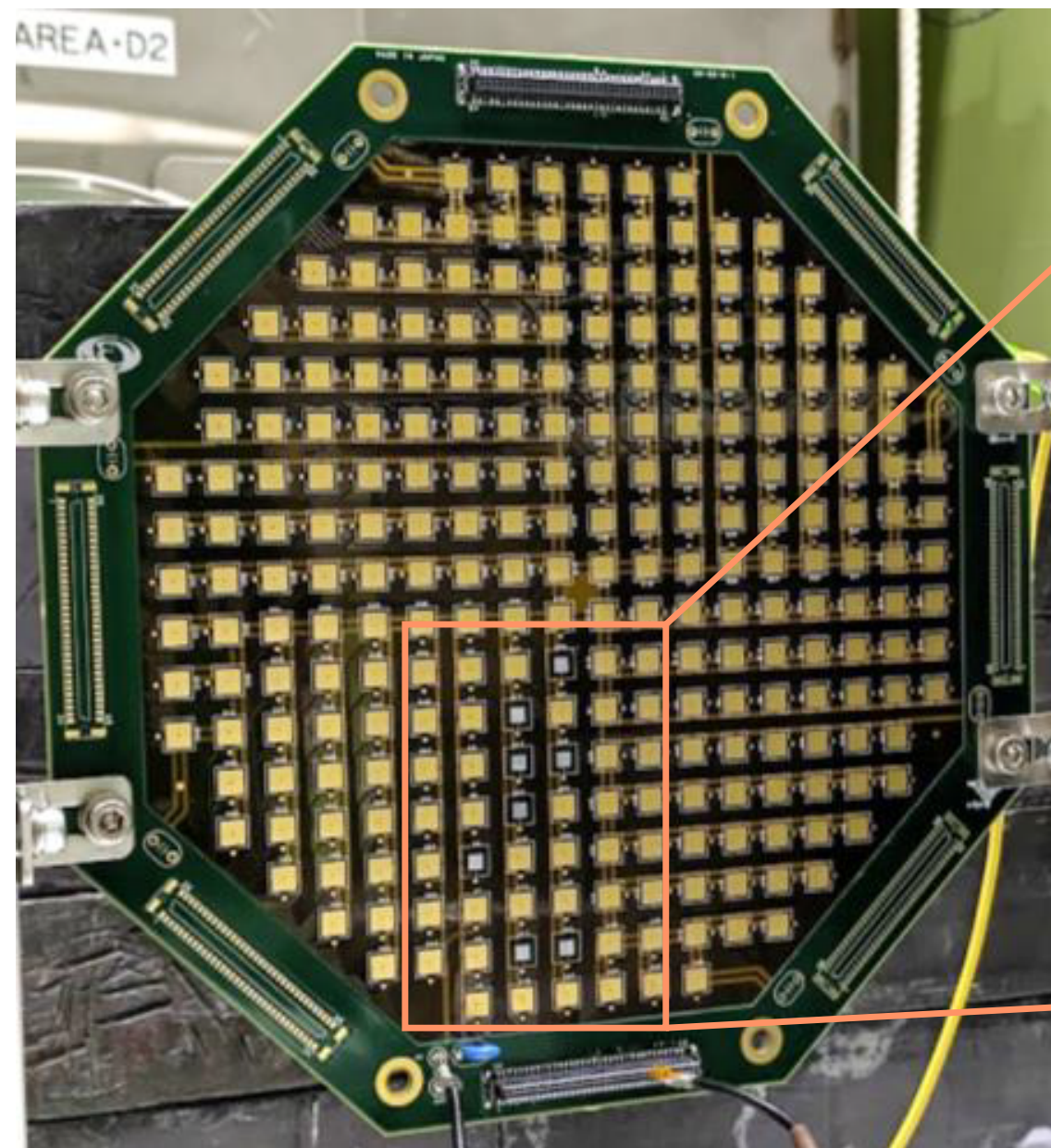
- Center region is thin Kapton board. Edge region is normal board to support the center region.
- Signal wires run between SiC sensors.

Q_{sig} : 75 MIPs (11 ke-/MIP), continuous waveform digitizing in 10 MHz.

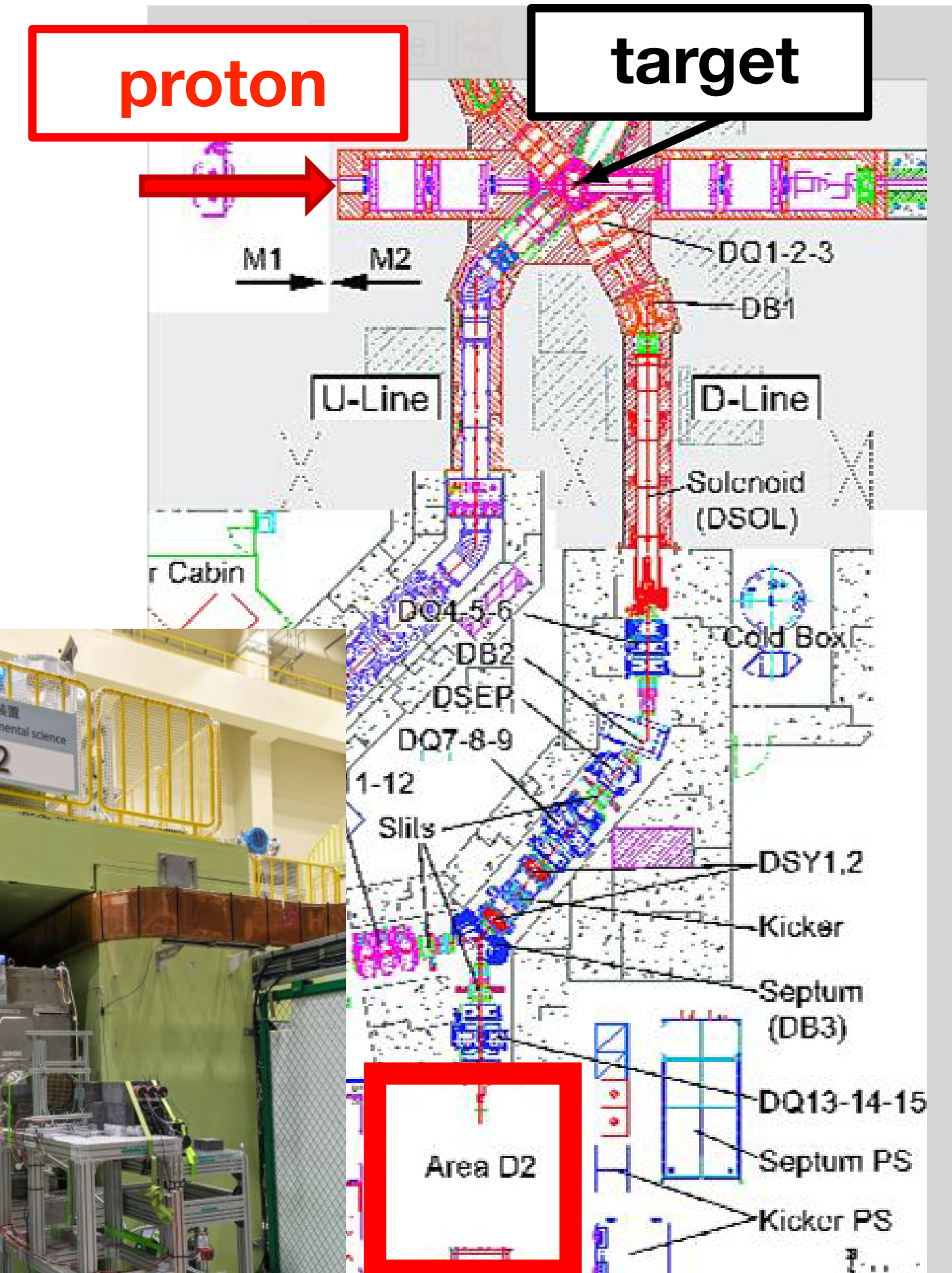
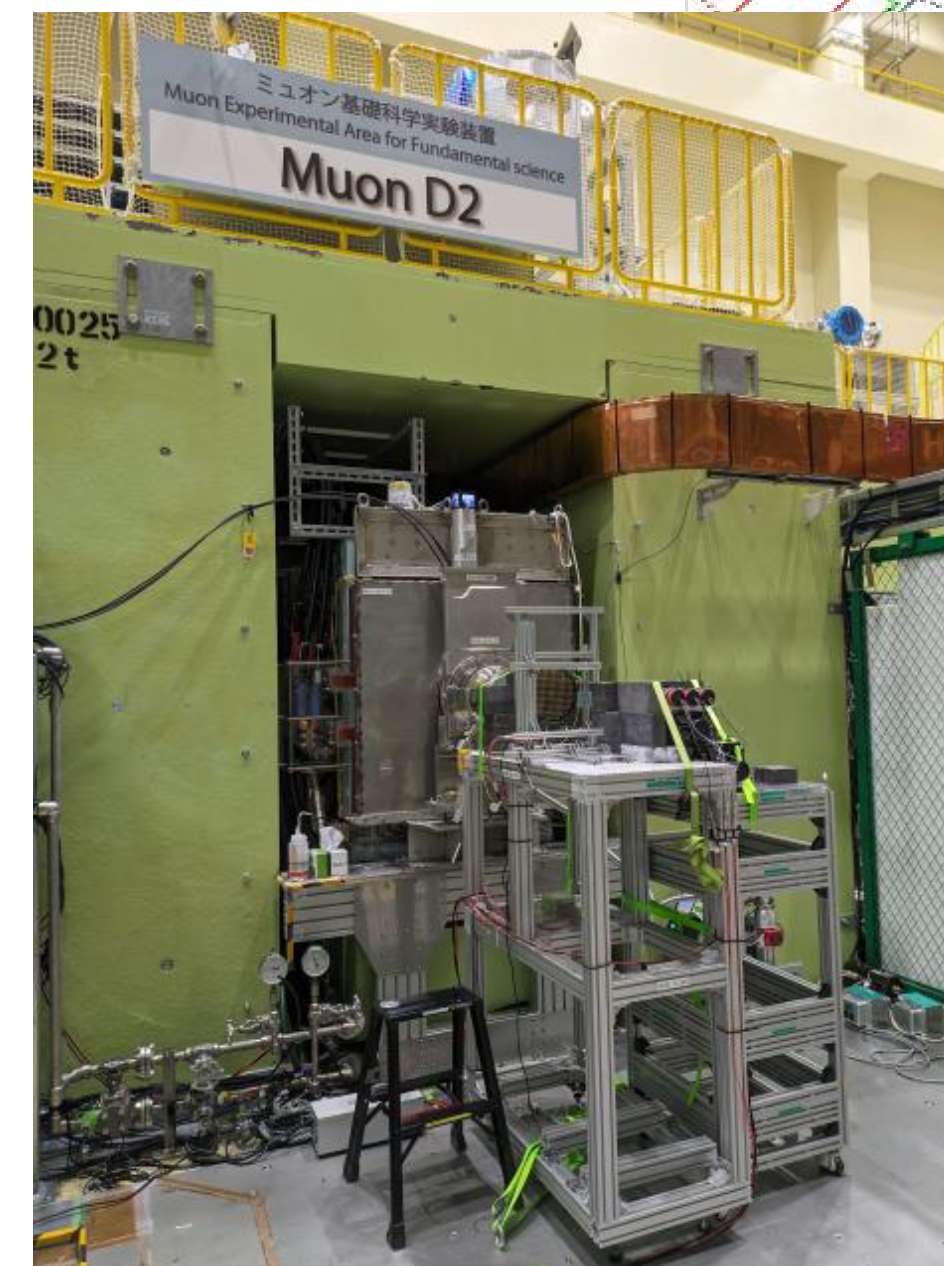


Beam test results

- MLF (Materials and Life science experimental Facility), D2 beam line
- Pulsed muon beams (25 Hz, ~20 muons/bunch), 20~100 MeV/c.
- Very close to the actual experiment
- Readout electronics not ready in time for this beam test...(commercial CSA+shaper)



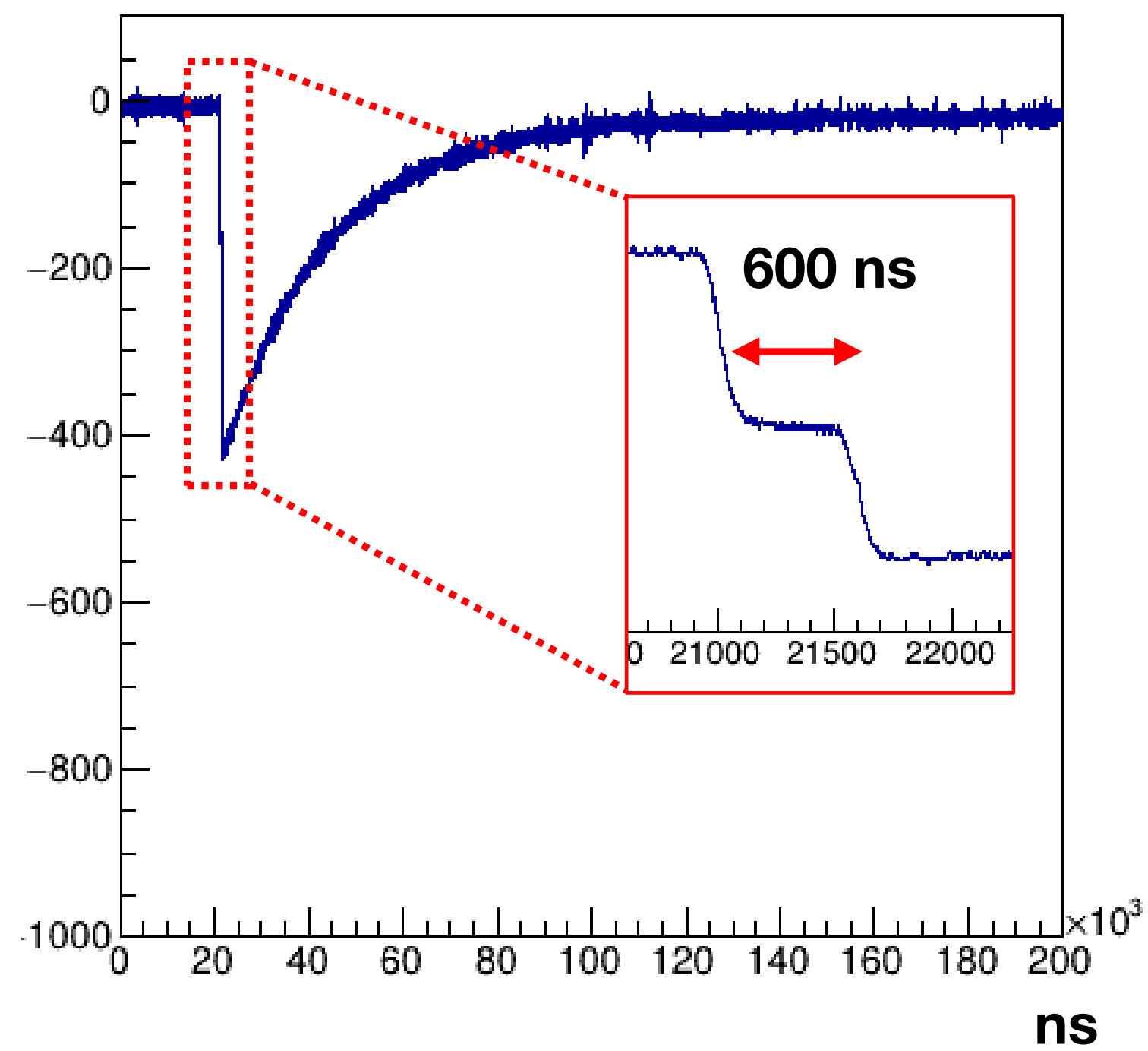
solder paste + Au wire



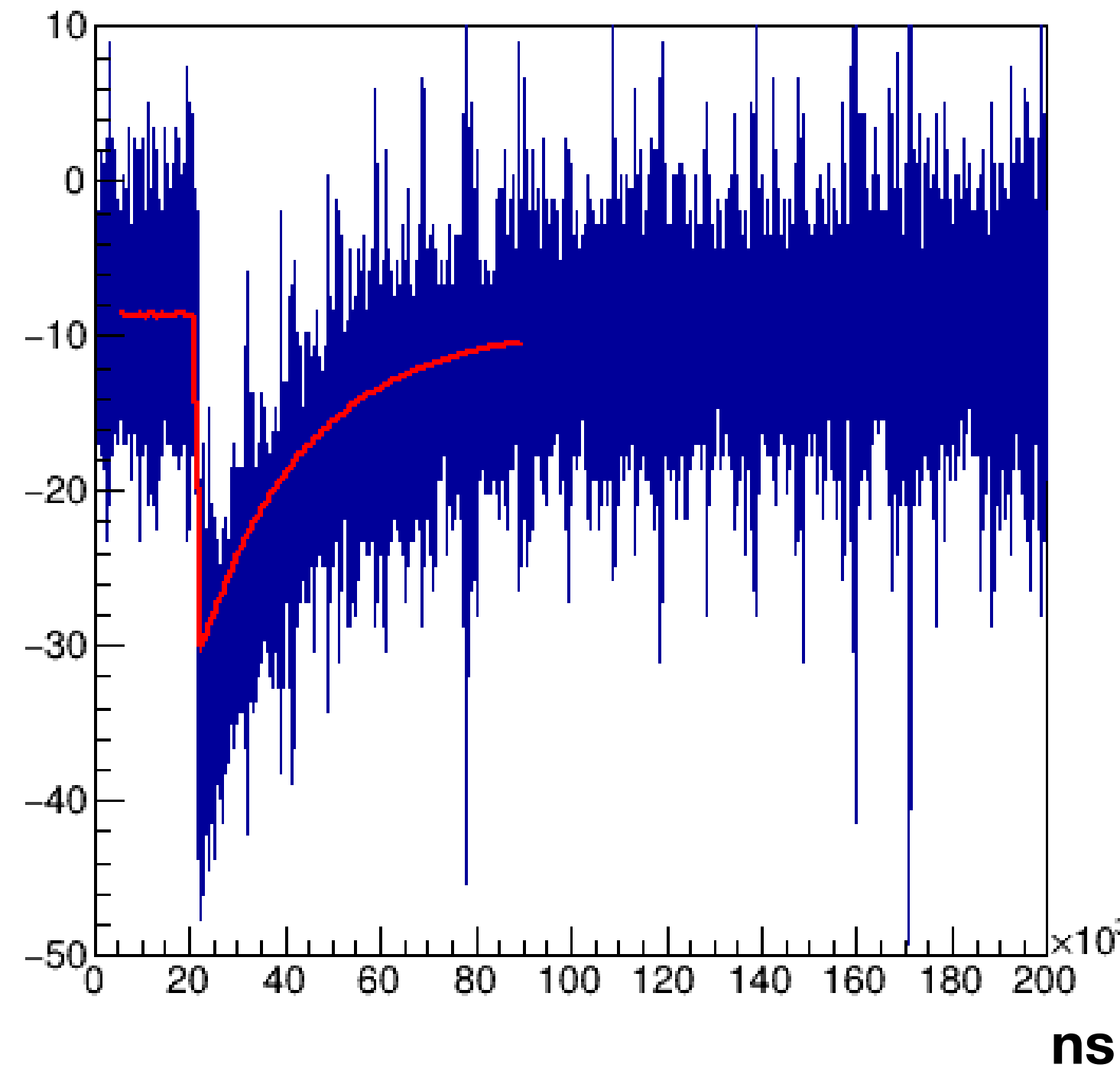
Signals from SiC sensors

- Triggered by beam-injection timing

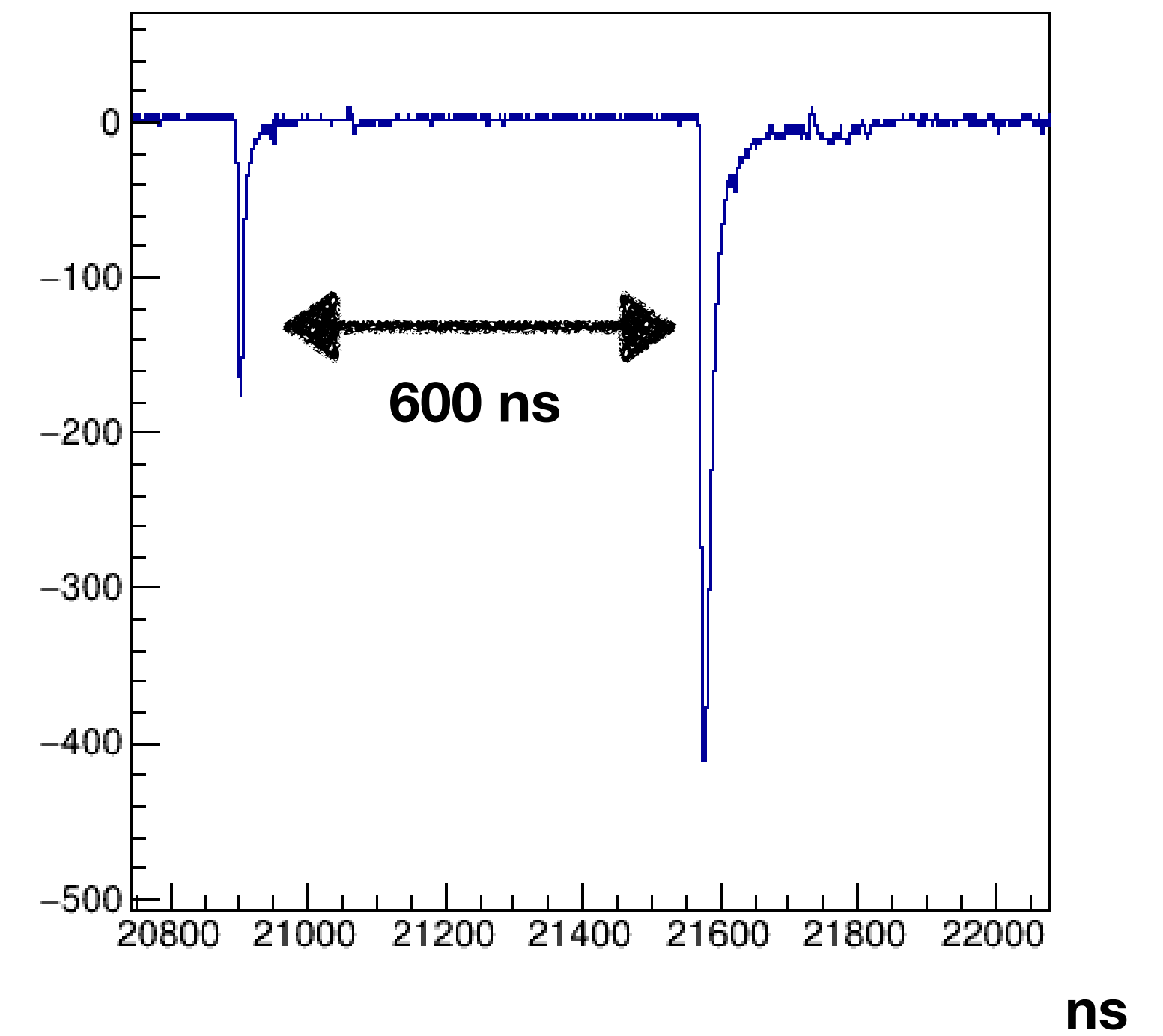
Signals from SiC (>10 muons)



Signals from SiC (2-3 muons)

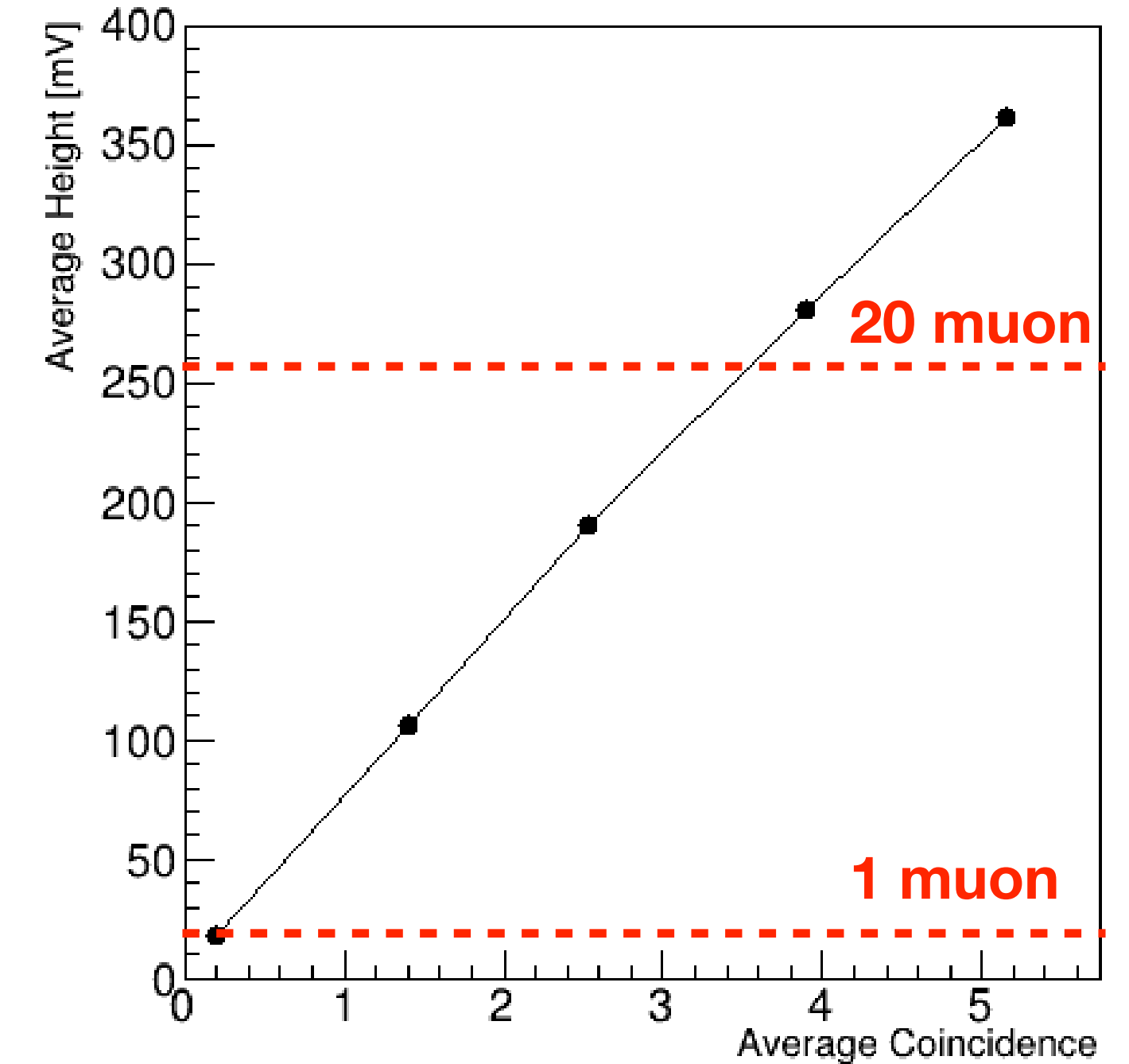
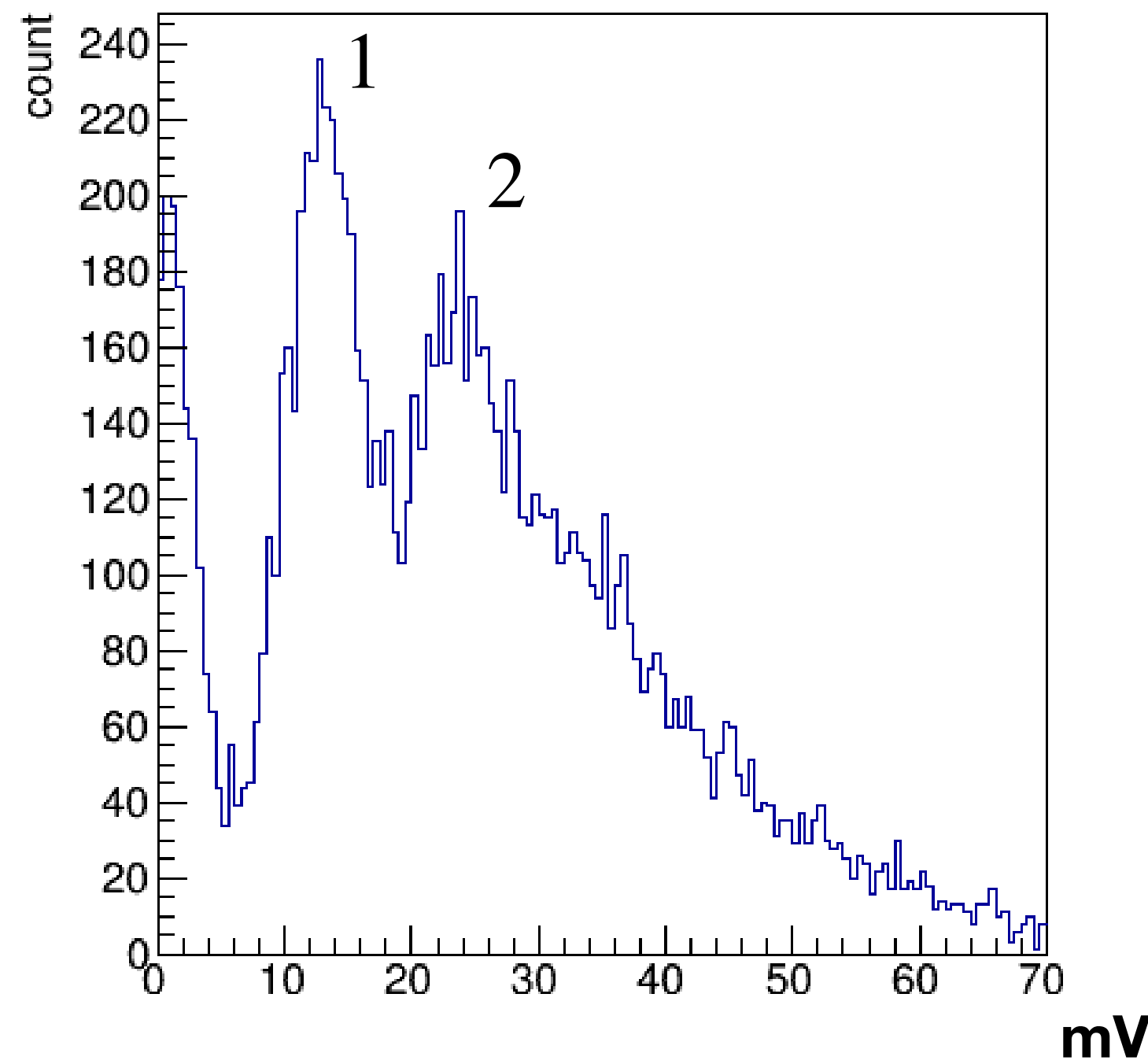
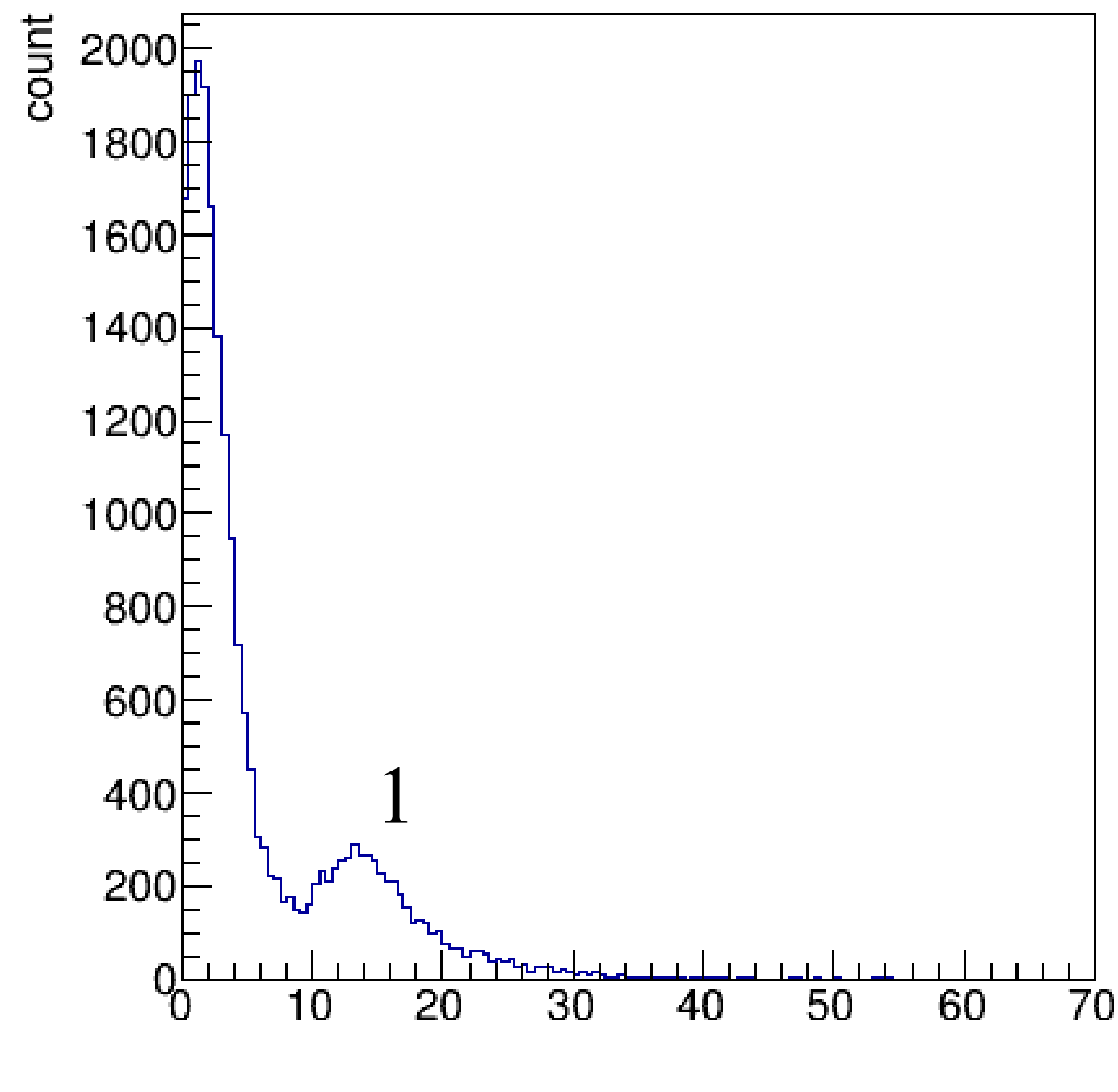


Time structure of muons
(double pulses/bunch)



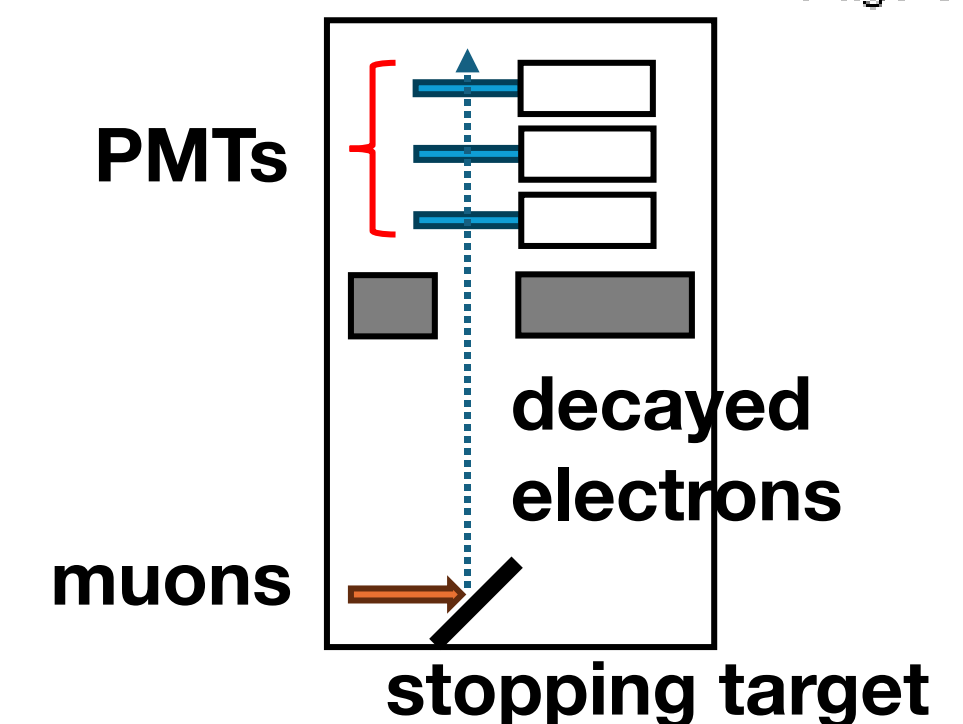
Pulse height distribution@ low intensity μ -beams

@lowest intensity beams



- Discretized peaks (like photons)
- Pulse height determined by fitting, ~ 13 mV/ μ on
- Linear correlation with electrons, up to 30 μ ons

SiC sensors are ready for the muon beam monitor.

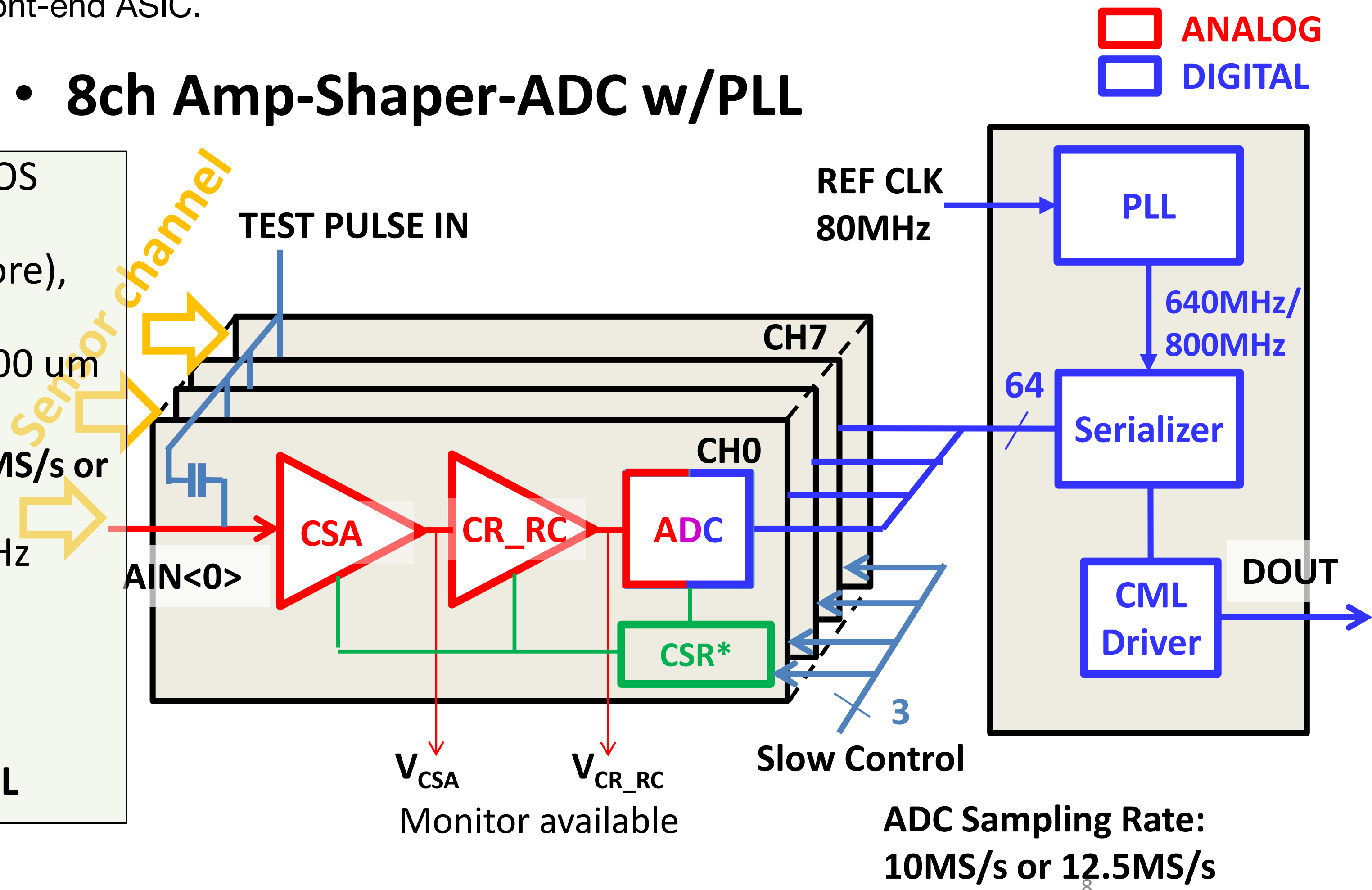


Readout electronics (SCIBER, Silicon Carbide IC for beam monitor)

Radiation-tolerance also required to front-end ASIC.

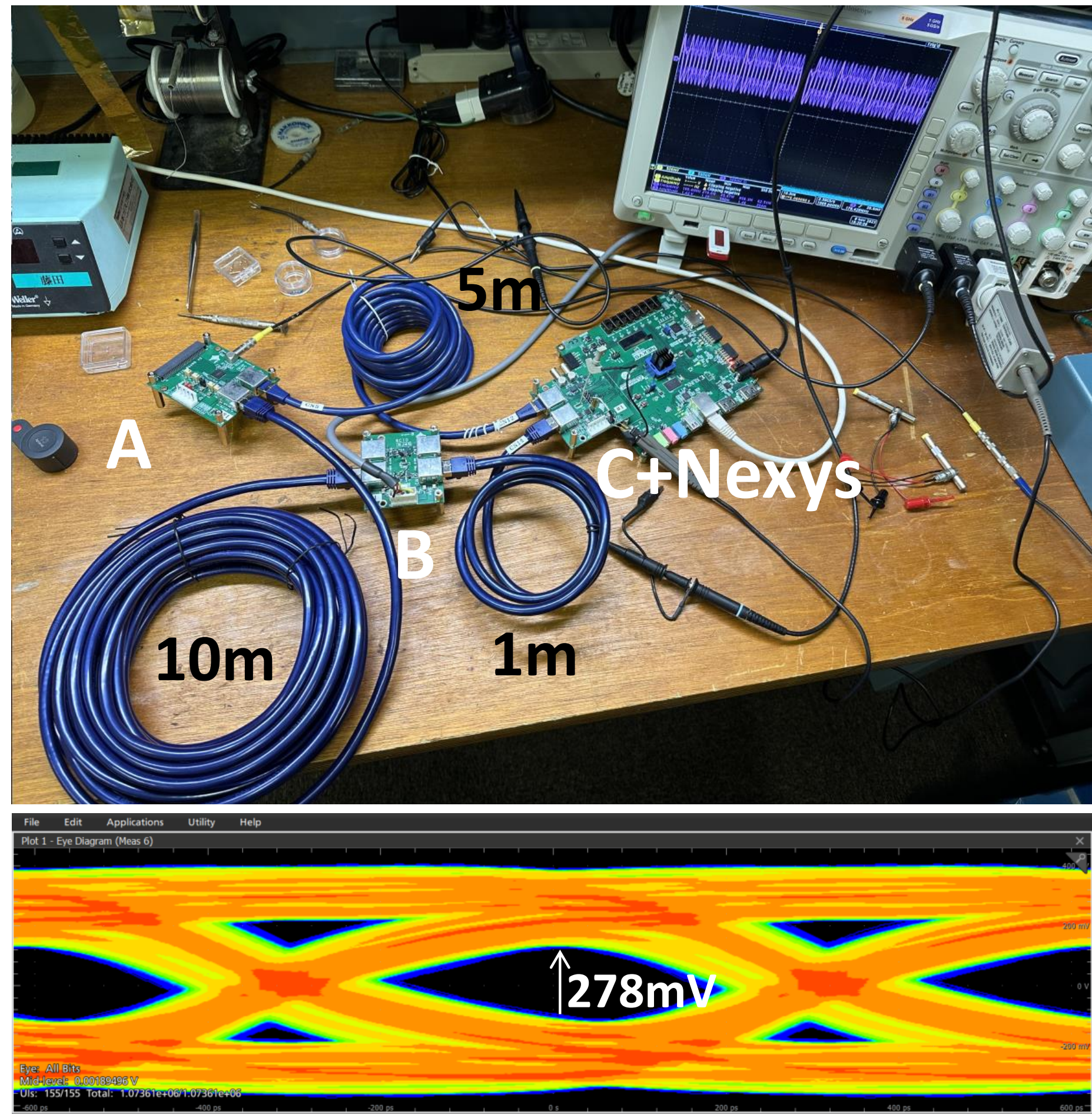
• 8ch Amp-Shaper-ADC w/PLL

- Technology: TSMC CMOS 65nm LP
- Supply Power: 1.2V (Core), 1.8V (I/O)
- Chip size: 960um x 2,000 um
- 8-bit SAR ADC
 - Sampling Rate: **12.5MS/s** or **10MS/s**
- PLL: 800MHz or 640MHz (w/80MHz REF CLK)
- Inputs: 8 channels to connect sensors
- Outputs: Digitized differential signals, **CML**



Signal integrity test (ADC+CML)

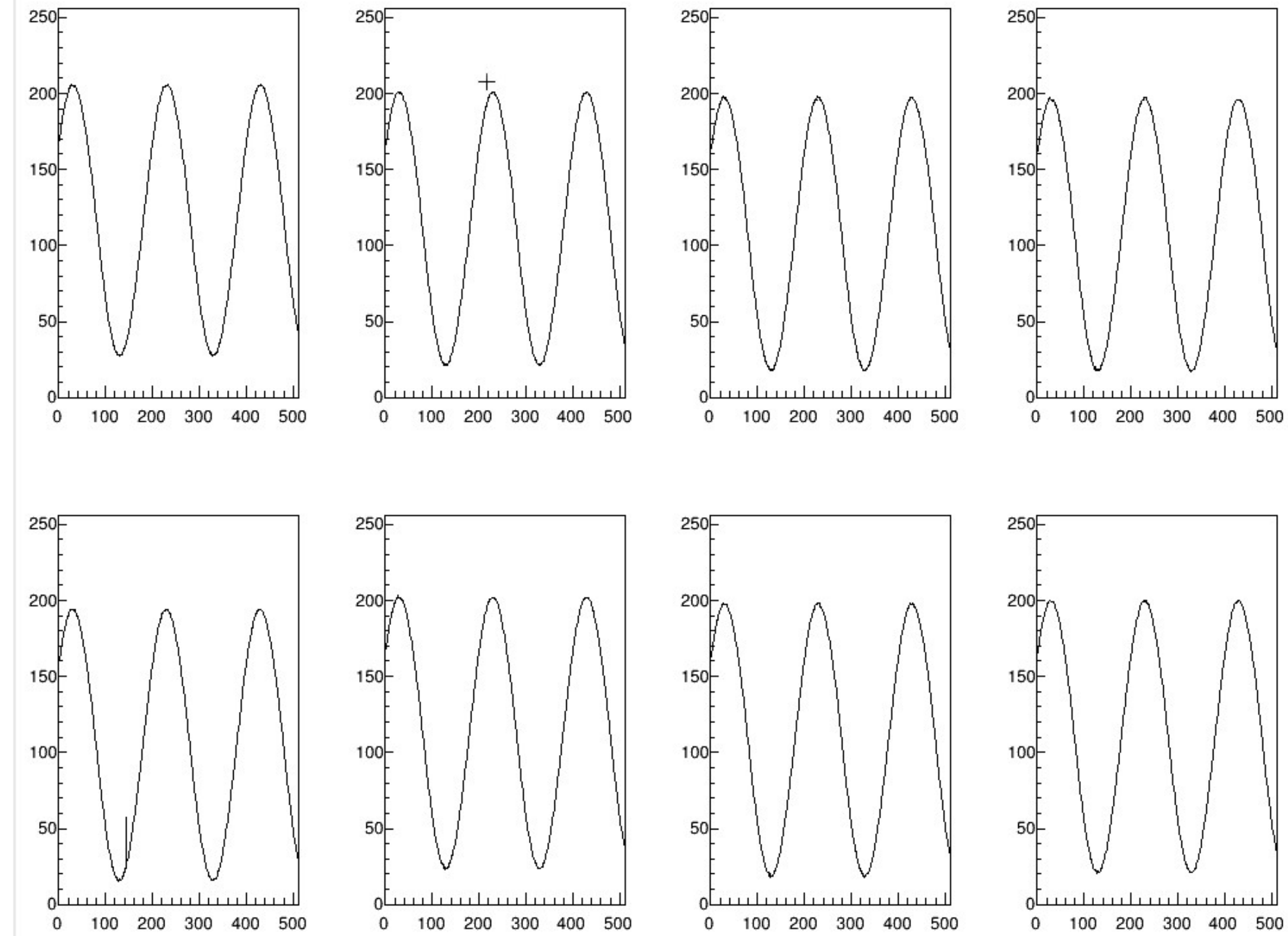
Cable length estimated as 10-15 m from μ BM to backend electronics.



640 Mbps
@10 m

Eye height: 275.7 mV, Eye width: 449.8 ps

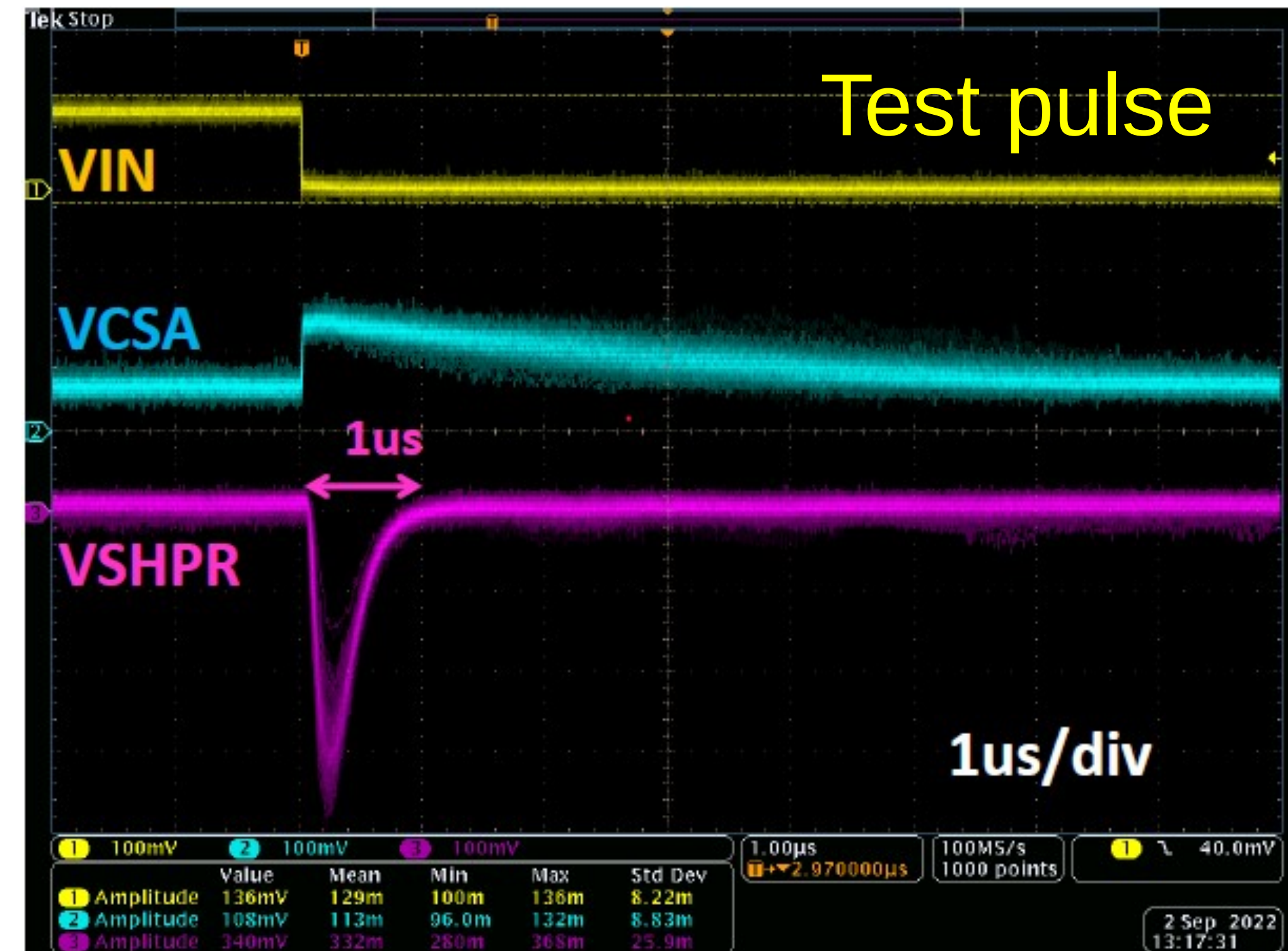
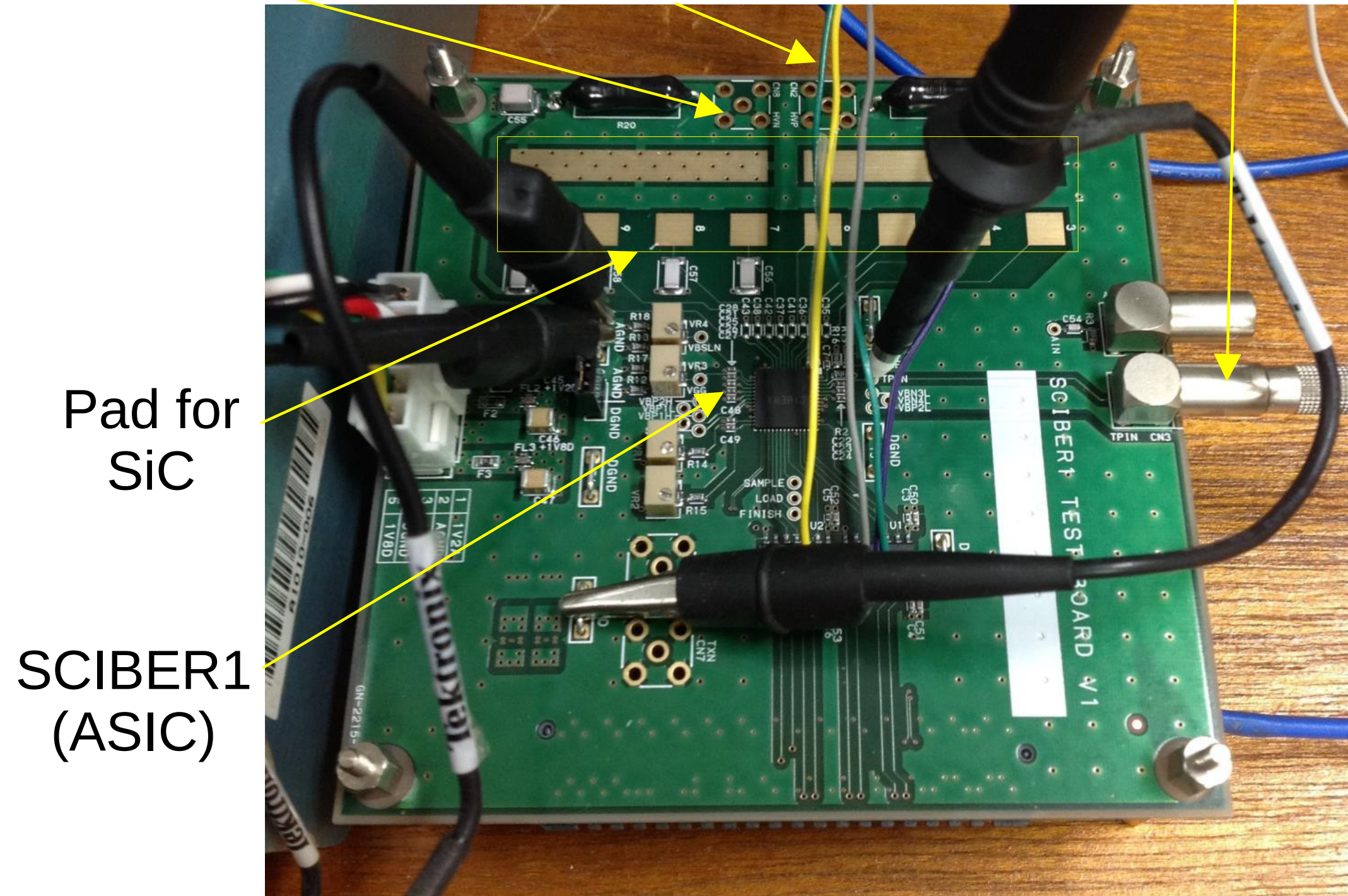
• @ Cable 10m



CML-TX is sufficient for driving 10 m cables.

Analog blocks (CSA+CRRC)

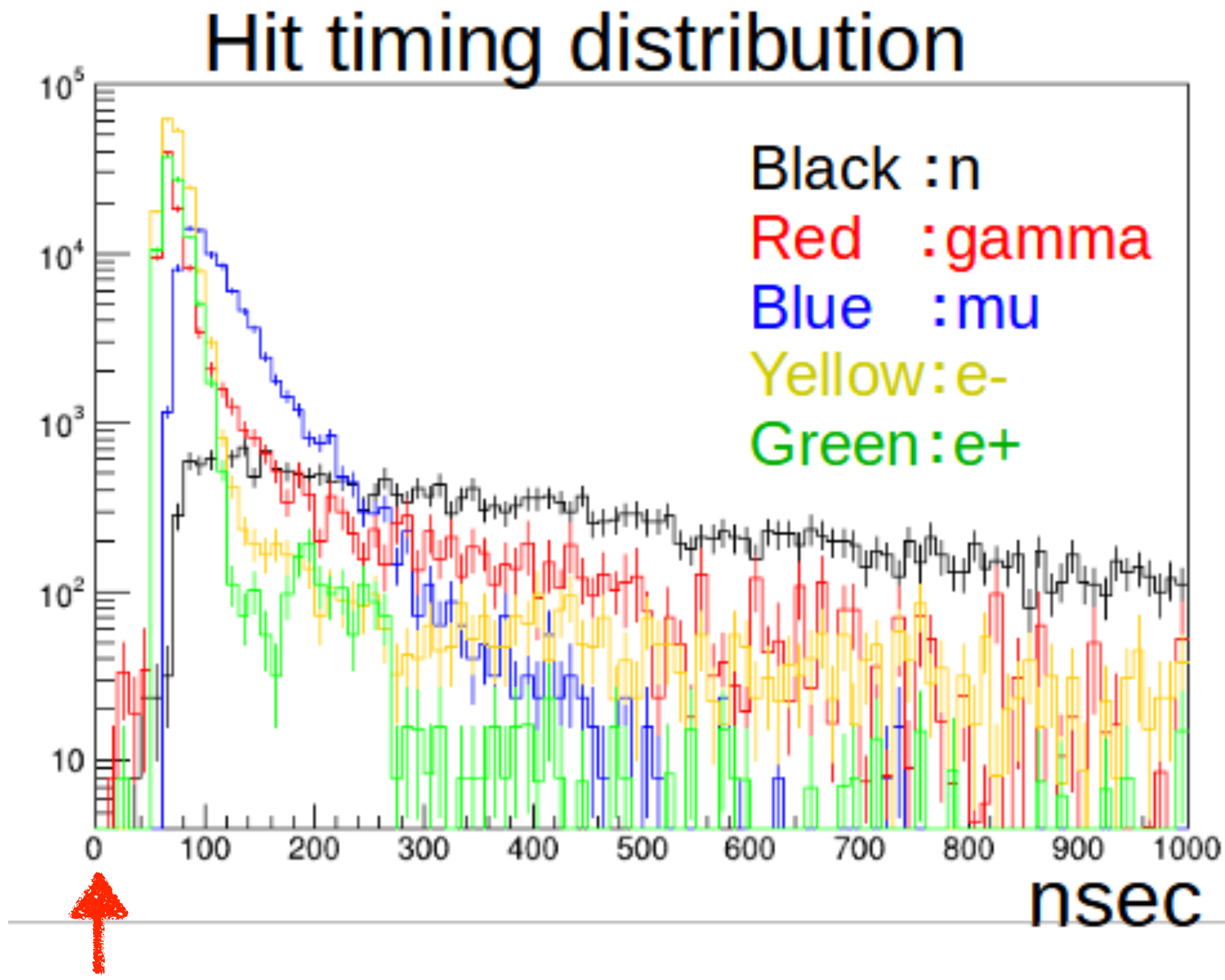
Pad for HV connector Wires for Slow Control Pulse Signal



- Analog blocks working, but we need faster shaping times.
- We changed the architecture from CSA to TIA in the 2nd prototype chip.

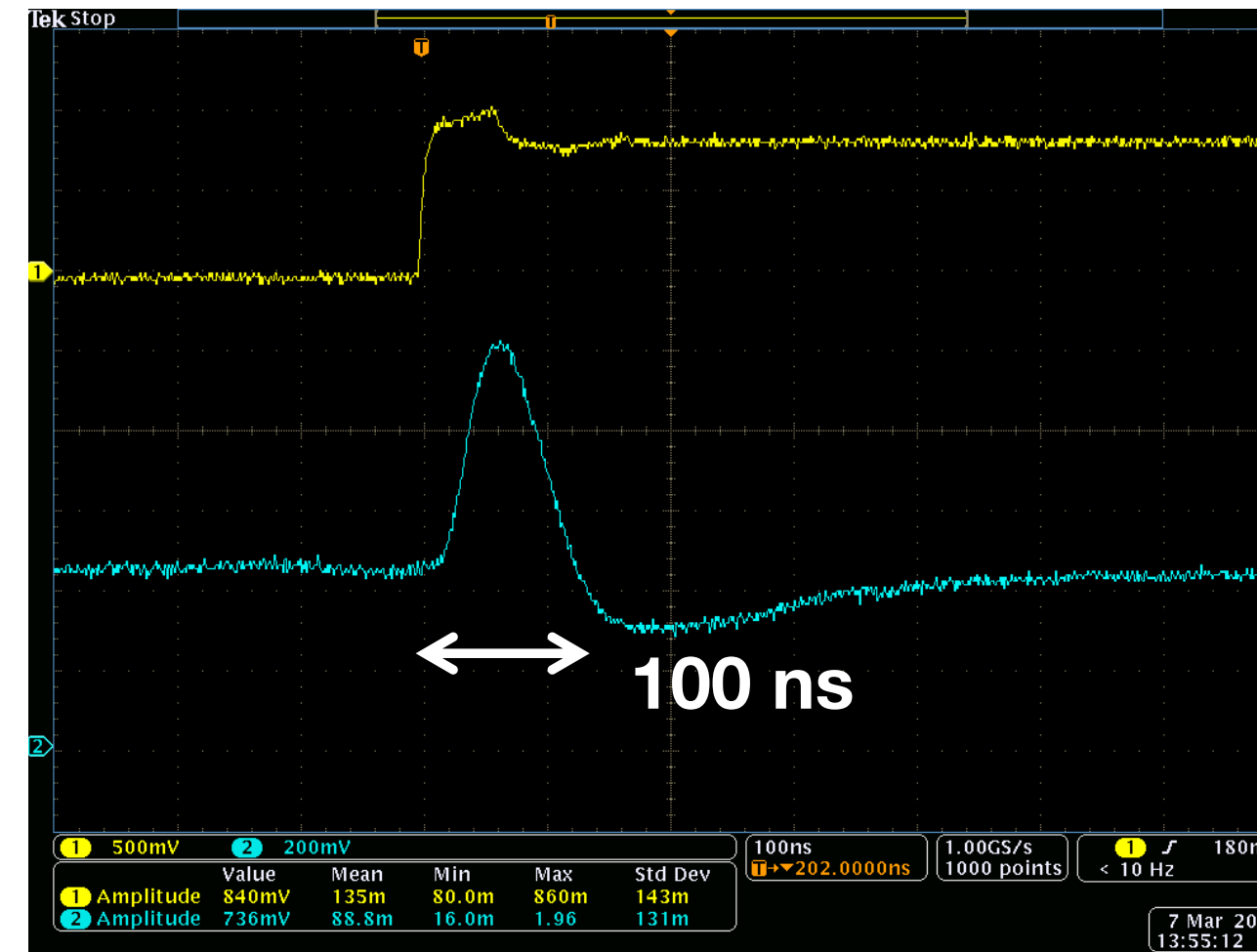
TIA+CRRC architecture

- 2nd prototype ASIC is under testing.
- **Fast shaping time of <100 ns** required since muons arrive at 100~300 ns in the hit timing distribution.

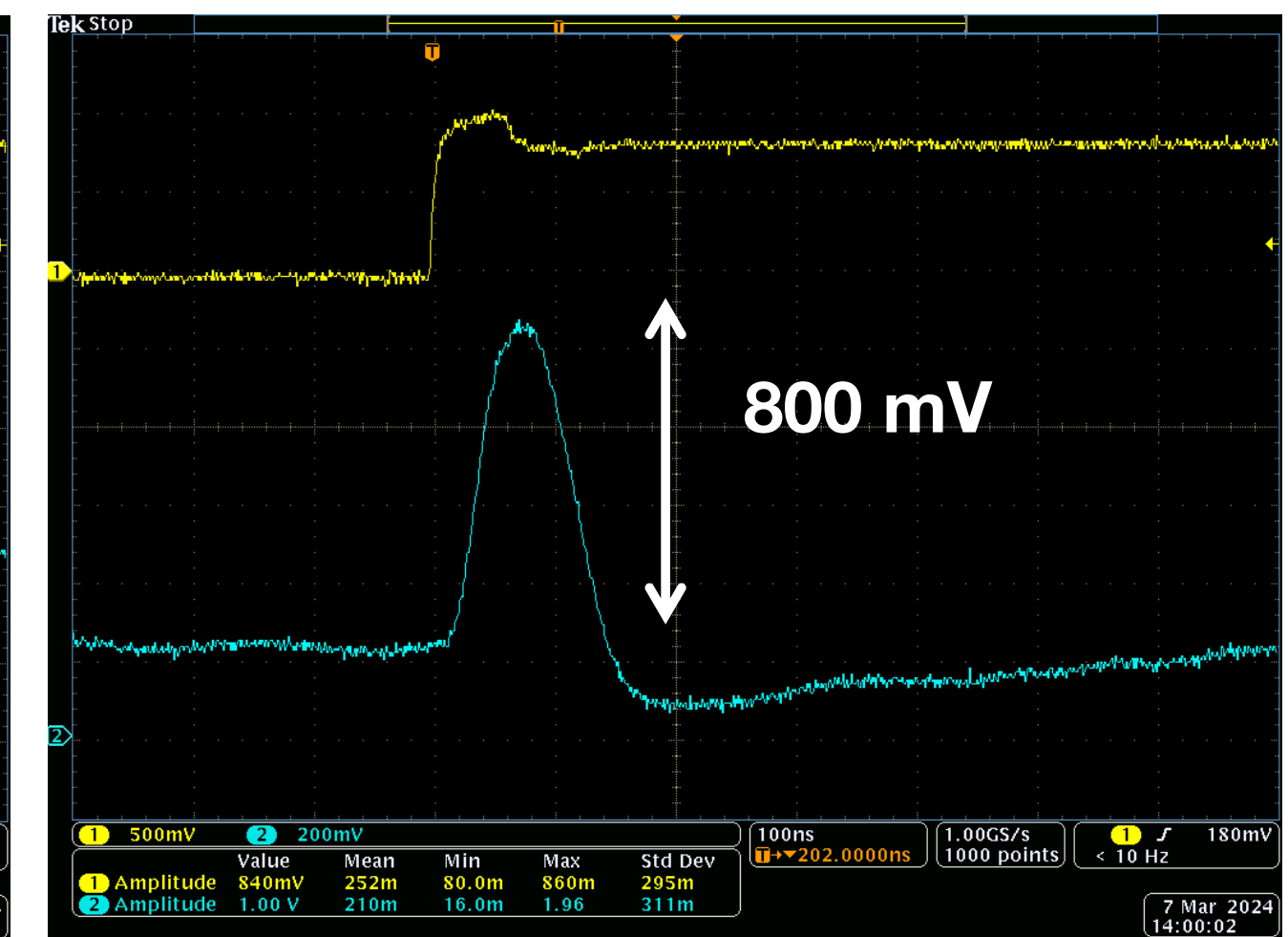
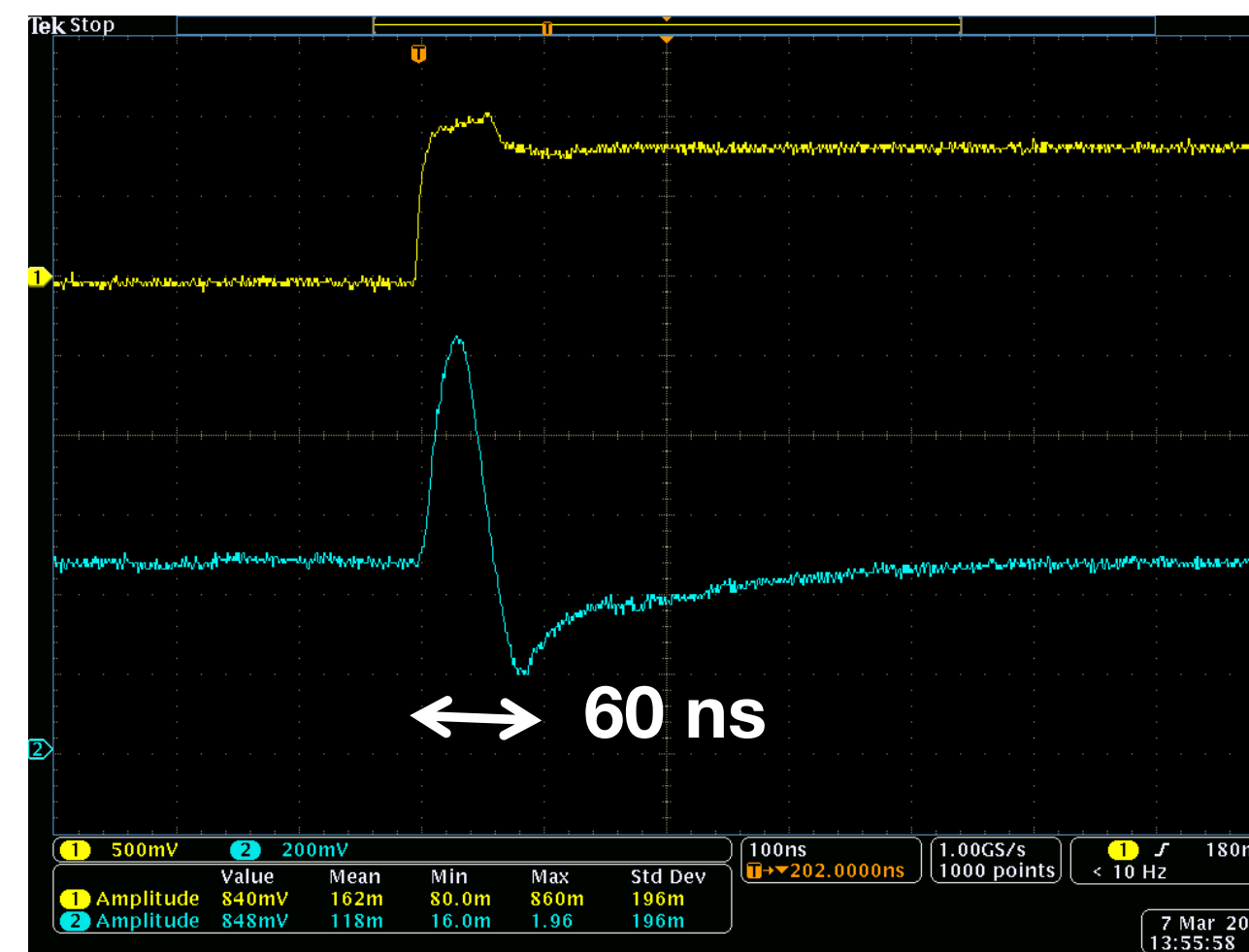
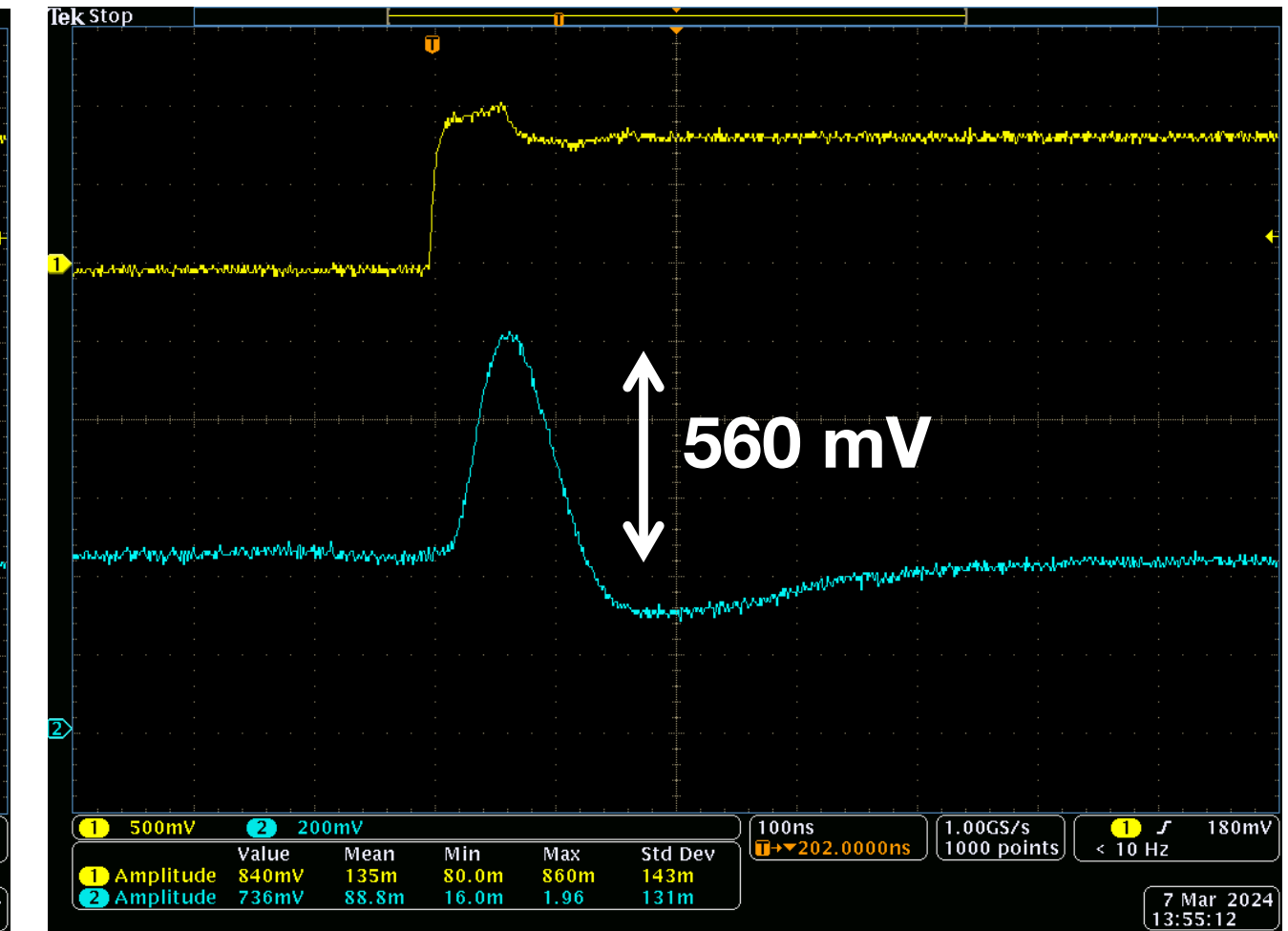


Bunch timing with every 1.17/1.75 us

Variable peaking times



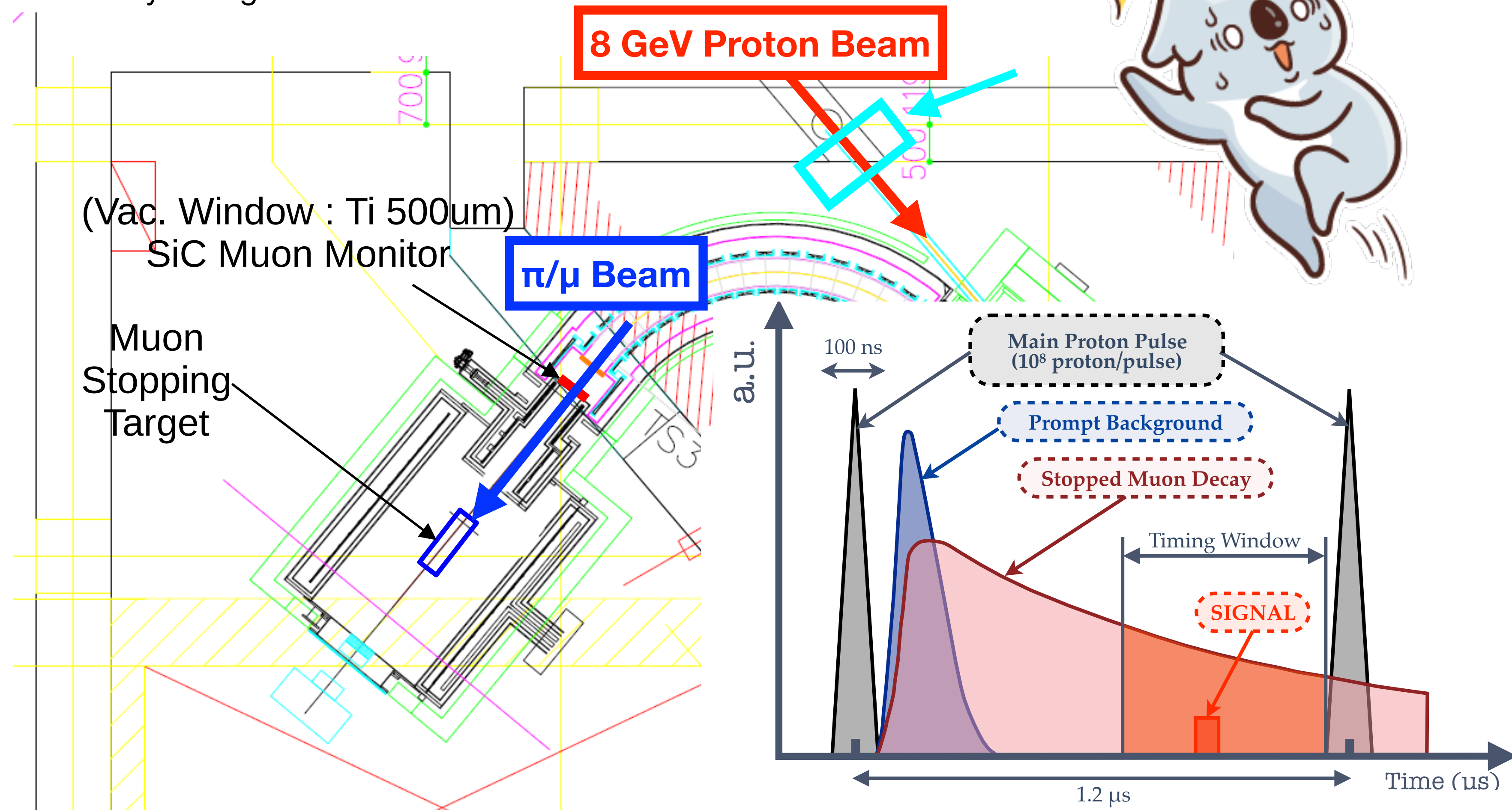
Variable voltage gains



We submit the final ASIC in this December.

Further Demand for SiC sensors (more challenging)

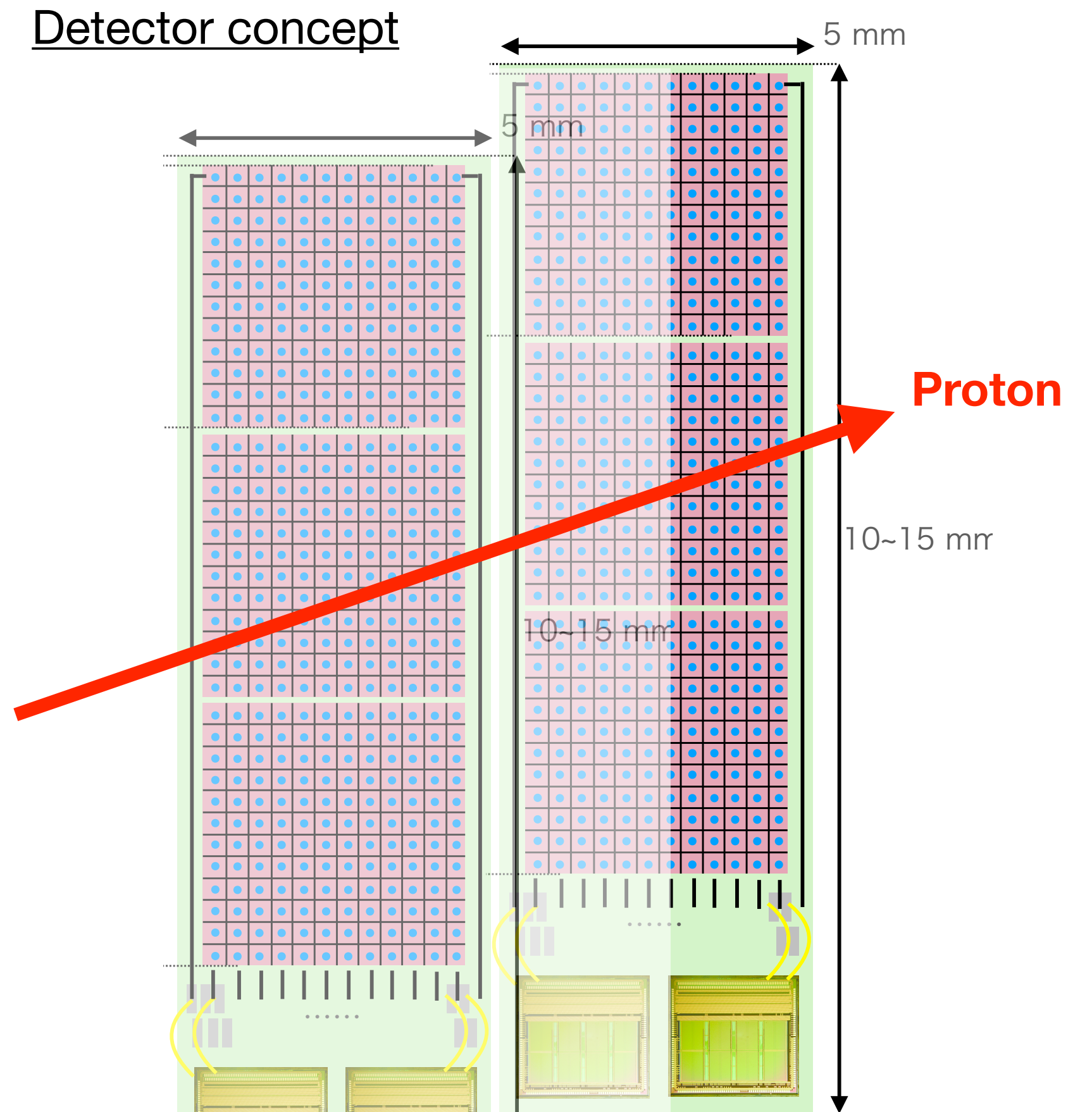
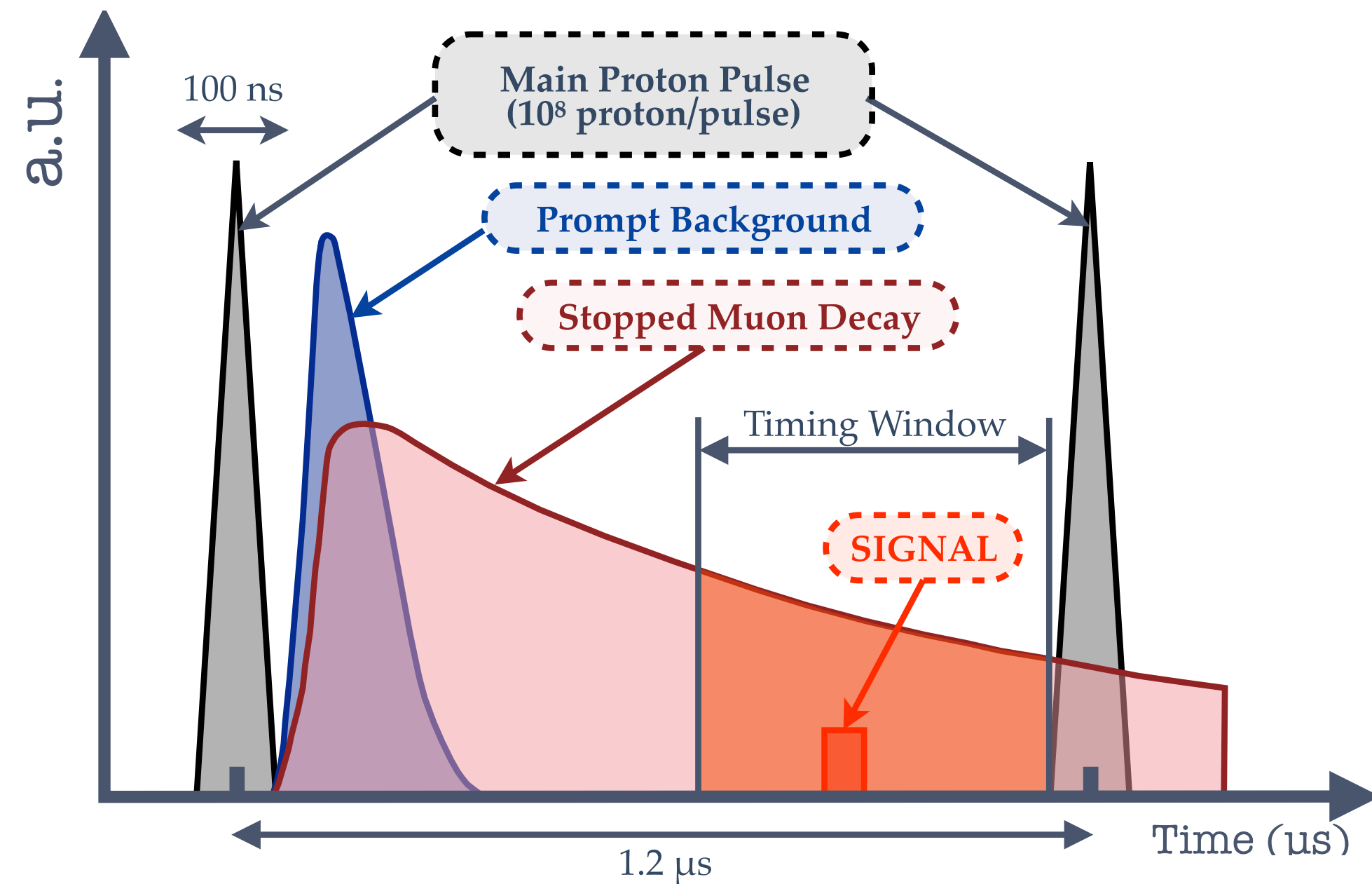
- 8 GeV proton beam is bunched in every 1.2 μ s.
- Pion is BGD. Select muon events by timing difference.



Want to confirm no leaky protons (extinction) between bunches. \rightarrow **On-axis** beam monitor with SiC!

Requirements for Extinction Monitor

- Want to detect 1 proton after the main bunch
- Max. 1.6×10^7 proton/bunch with beam spot of $\phi \sim 1$ cm (TBD)
- Neutron fluence of 2.1×10^{14} n_{eq}/cm² during Phase-1



- Need larger active area (~ 1 cm x 1 cm)
- Segmented electrodes (**pixels or strips**) to reduce event rates
- Dedicated electronics with timing-gate structure

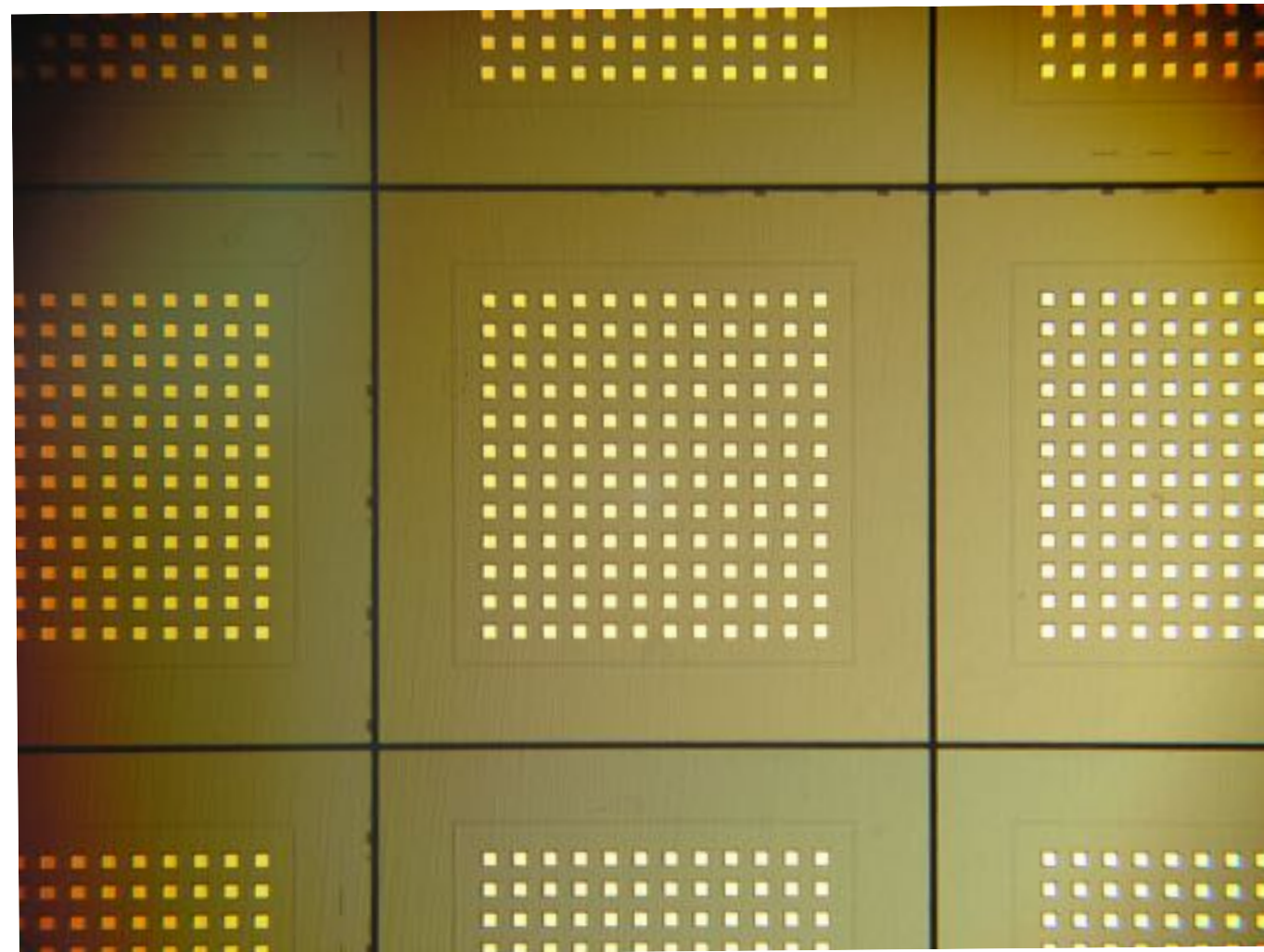
see the Poster, "The GAROP-2, a Radiation-Hard ASIC for Particle Beam Monitor Readout of the COMET Experiment", by X. Xu

To prove the concept, we investigated the **sensor segmentation** and performance uniformity.

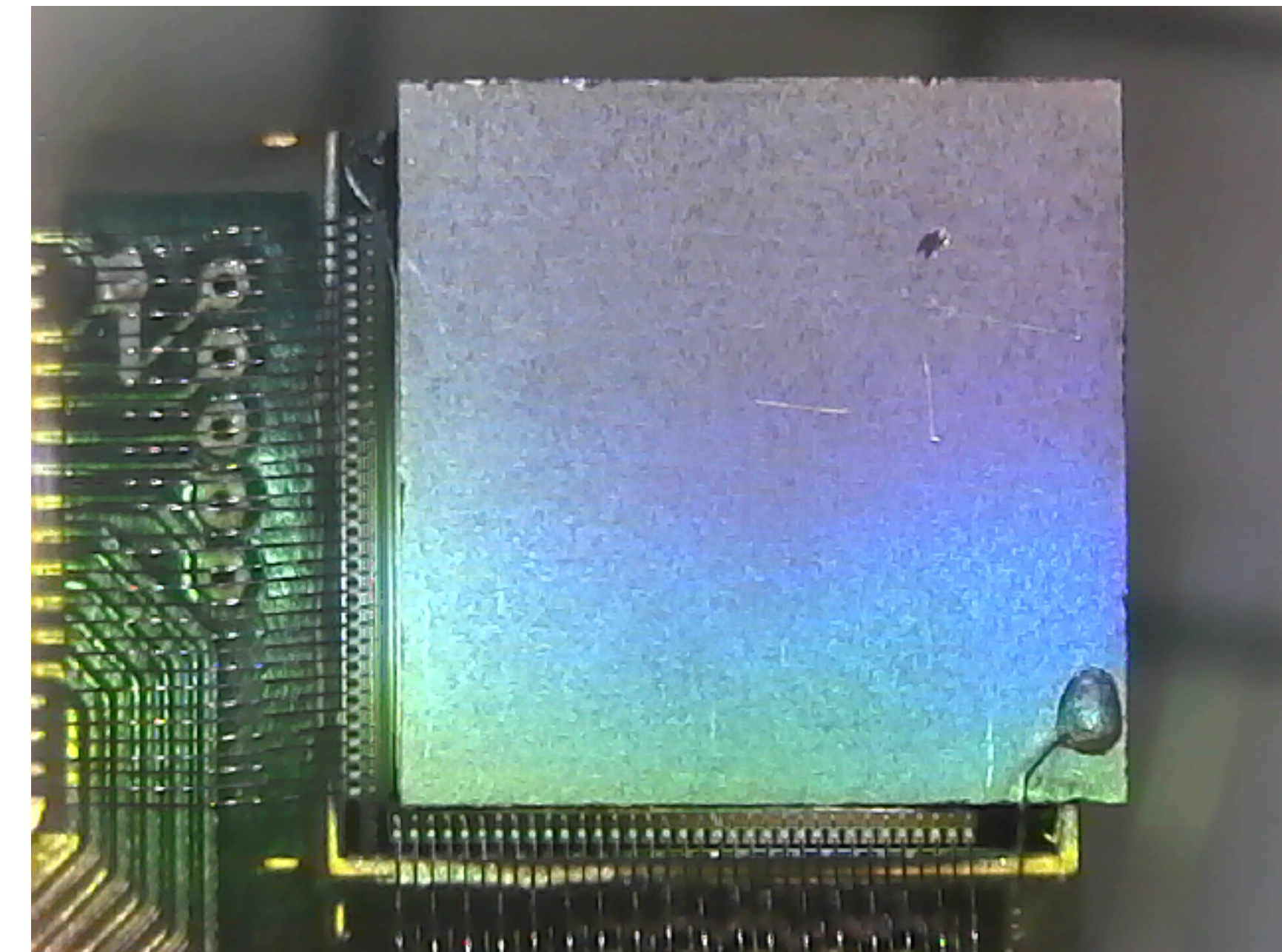
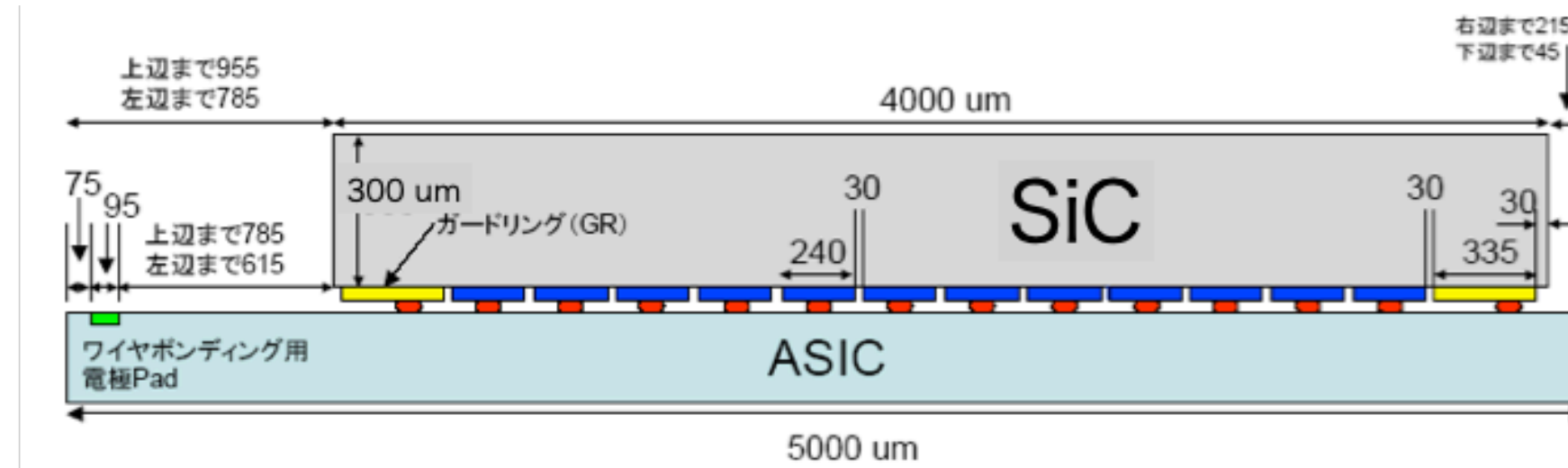
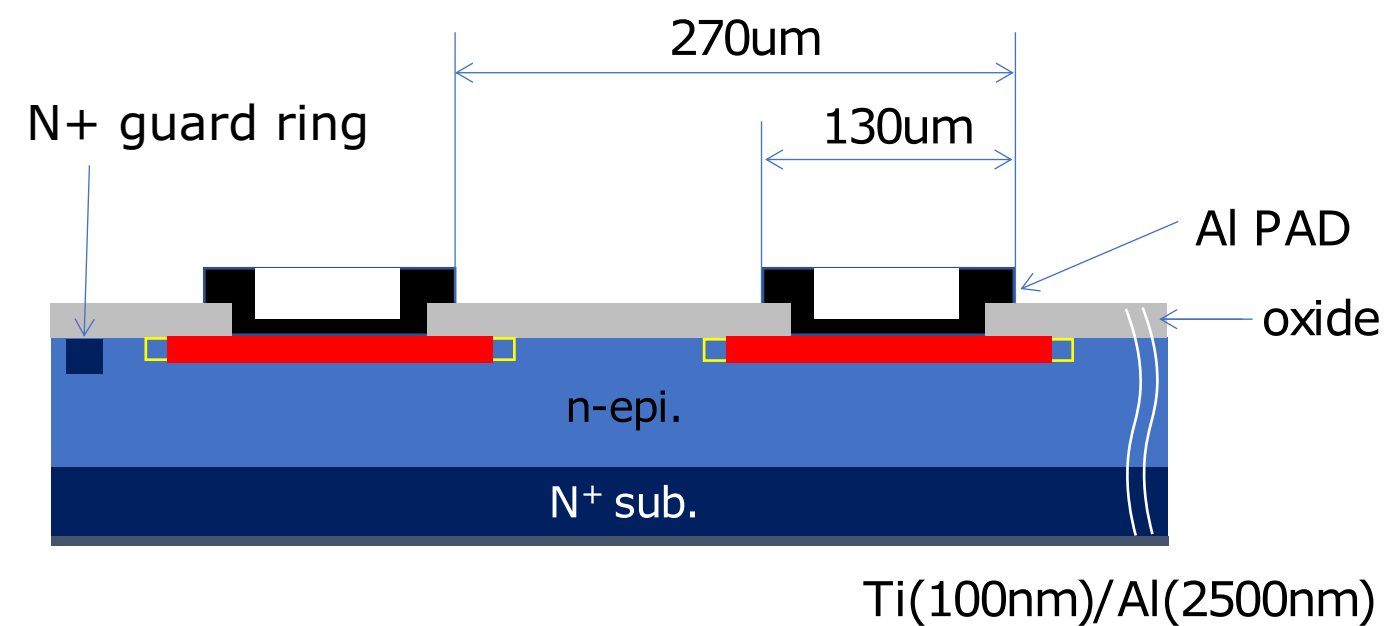
Sensor segmentation (hybrid pixel detector)

- 5 mm x 5 mm with 12 x 12 electrodes, 270 μm pitch
- readout with low-noise ASIC
- Au/In stud bump technology

(a)



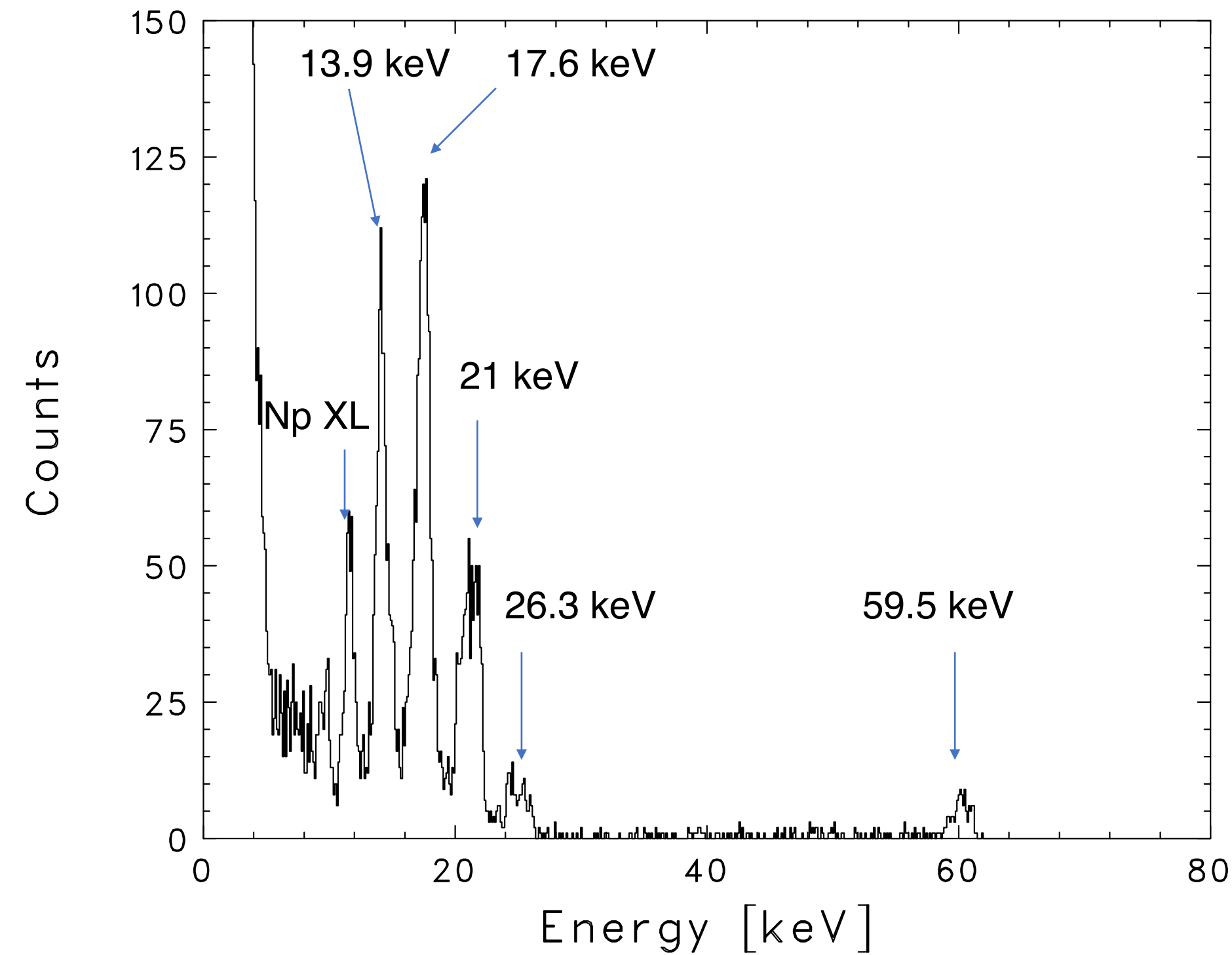
(b)



Passivation (Parylen or Silicone rubber) is necessary to prevent electric discharges @1 kV.

Spectral performance

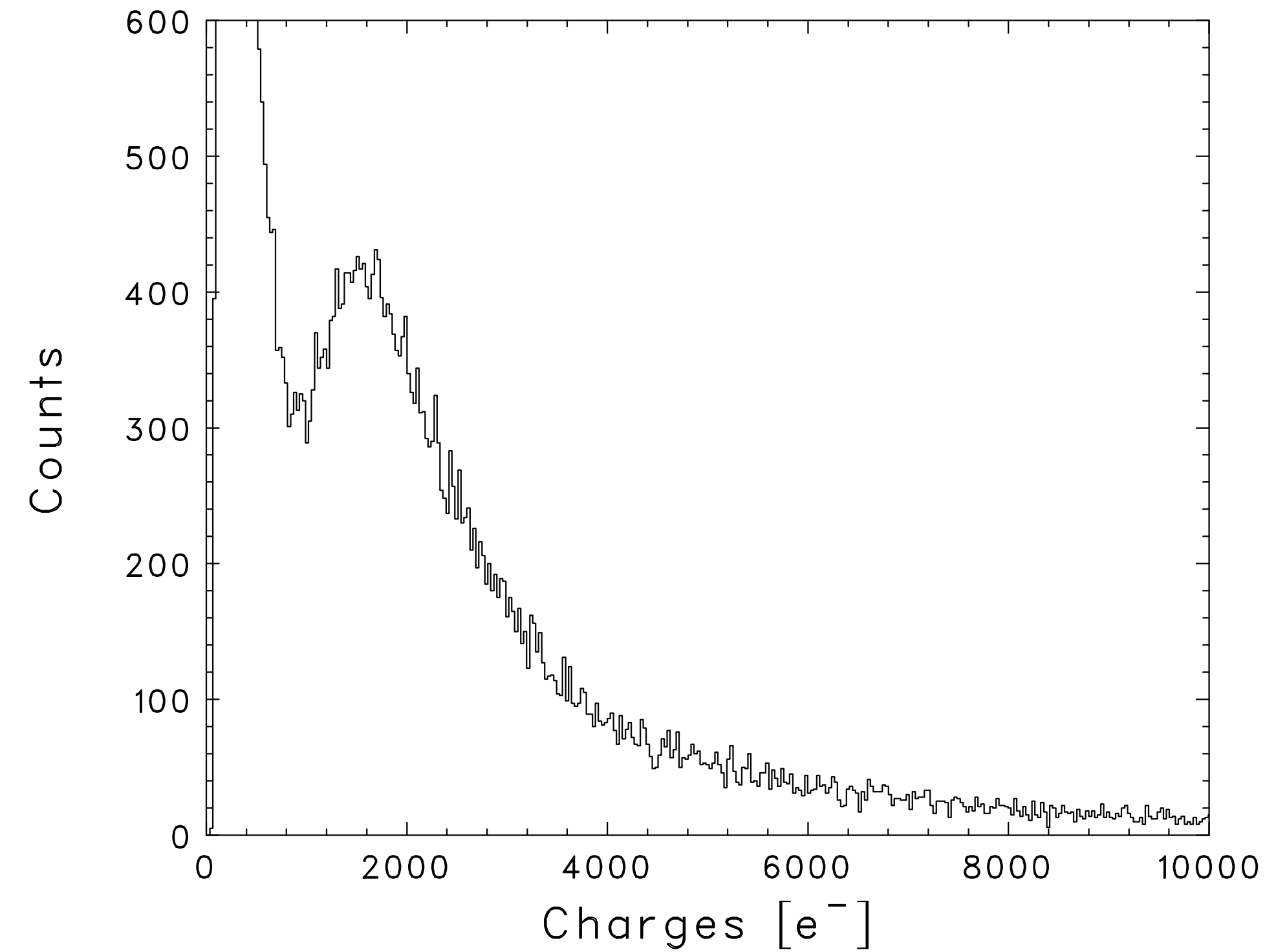
- HV: +600 V
- Exposure: 3 days
- Mode: HG



FWHM: 1.72 keV @17.6 keV

- HV: +600 V
- Exposure: 0.5 days
- Mode: HG

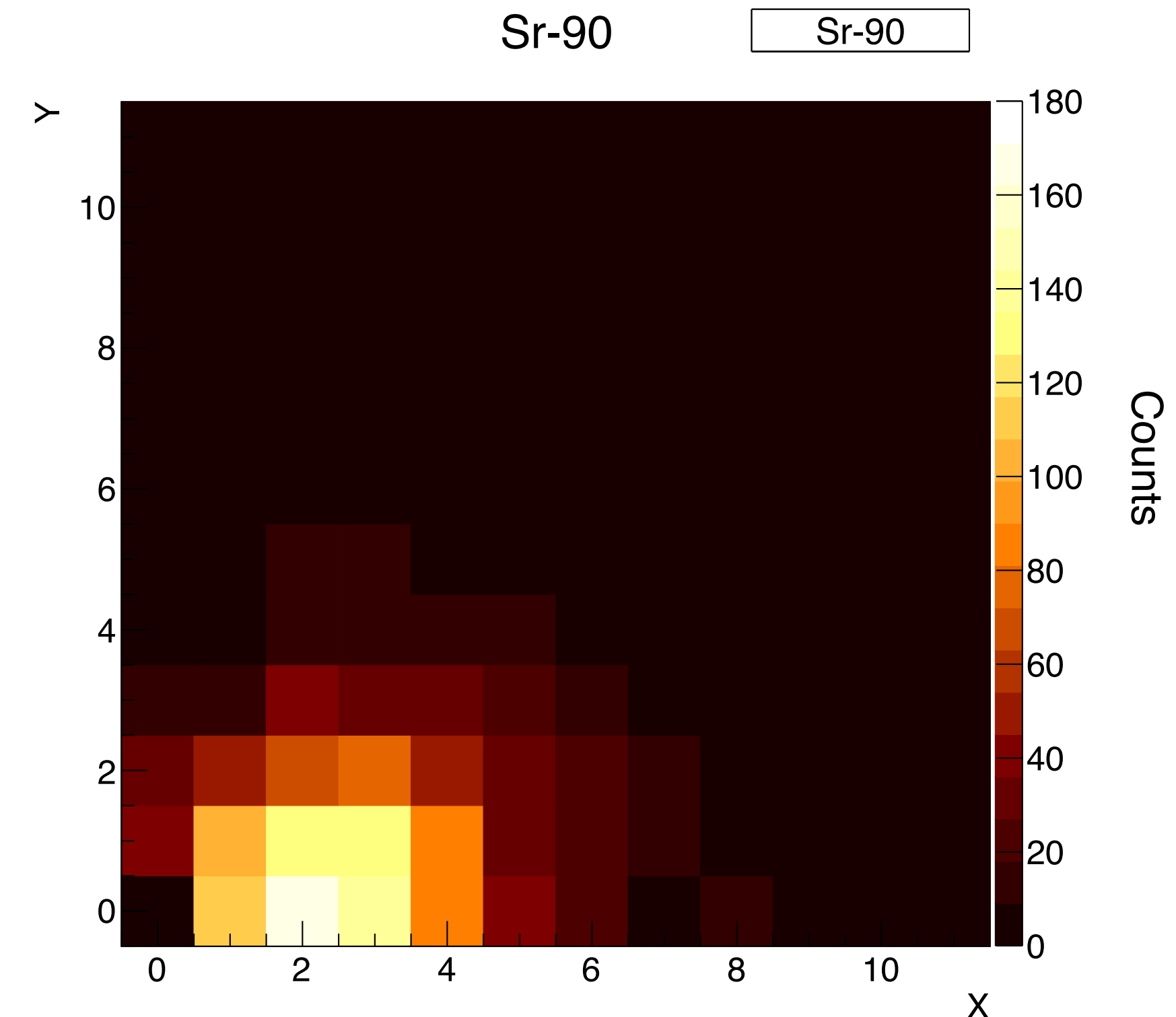
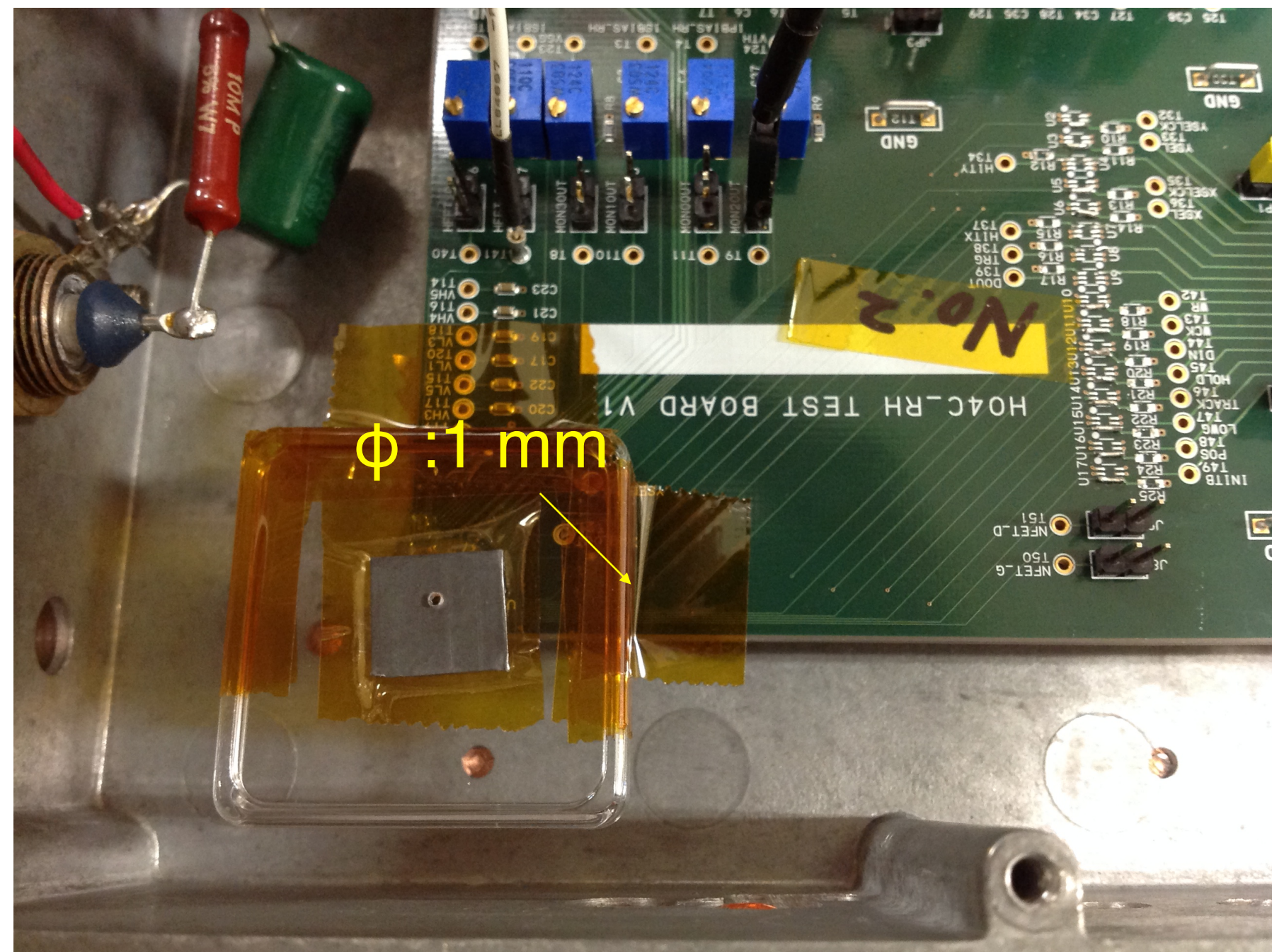
IEEE TNS, vol.70, p.1210, 2023.



Confirmed β -ray events from all pixels.

Imaging performance

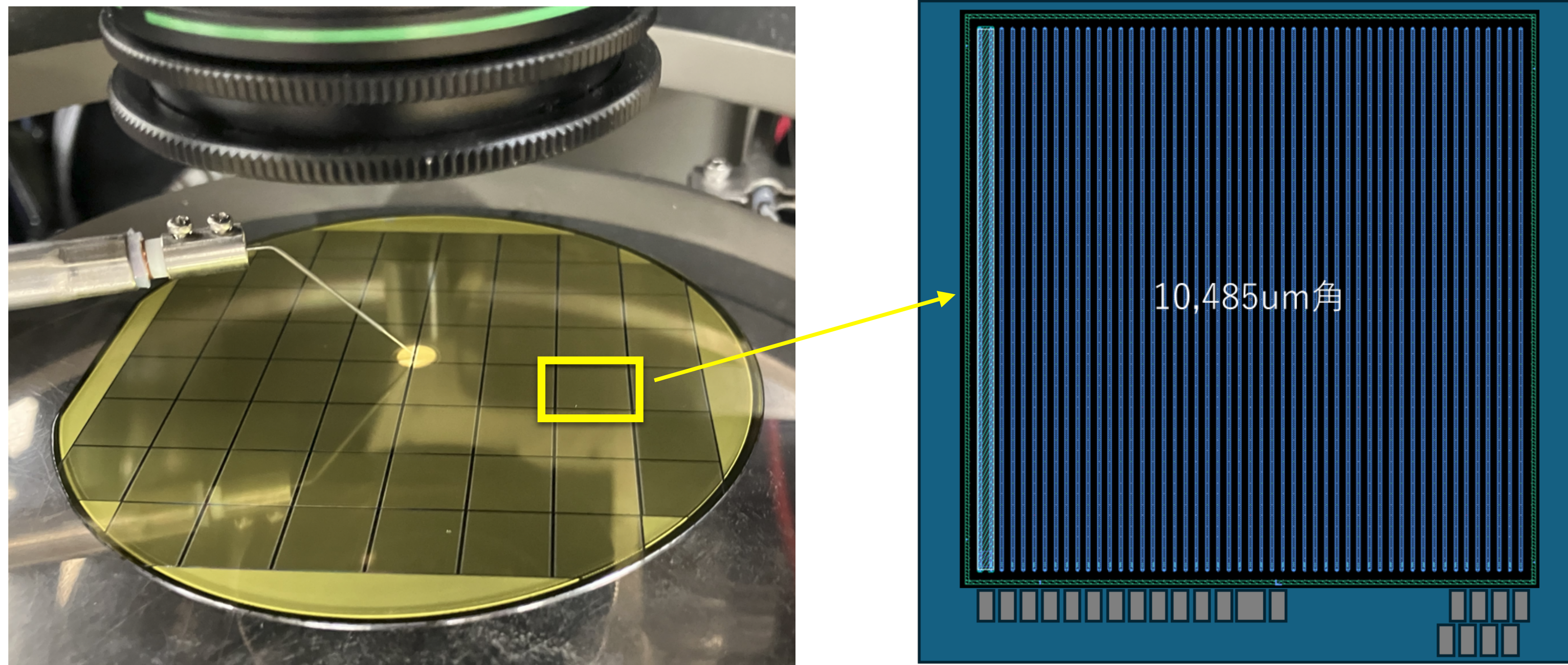
- Blind search of pinhole position in Pb sheet
- Count Sr-90 events between 1000-6000 e-, 1 min for each pixel



- Finer segmentation is realistic and nice uniformity expectable in larger devices
- SiC performance is closing to silicon.
- Still long way to realize the proton extinction monitor, but SiC is an important candidate.

Future prospect

For the extinction monitor, **SiC-strip sensor** (1 cm x 1 cm, 52 strips with 200 μm pitch) will be available soon!



Thank you very much for your attention.